POWER MODULE
PRODUCT CATALOGUE
模块产品手册

2020年08月第二版

扬杰科技
YANGJIE TECHNOLOGY

公司简介

扬州扬杰电子科技股份有限公司是国内少数集半导体分立器件芯片设计制造、器件封装测试、终端销售与服务等产业链垂直一体化（IDM）的杰出厂商。产品线涵盖分立器件芯片、整流器件、保护器件、小信号、MOSFET、功率模块、碳化硅等一揽子产品解决方案。

公司产品广泛应用于电源、家电、照明、安防、网通、消费电子、新能源、工控、汽车电子等多个领域。

公司于 2014 年 1 月 23 日在深交所上市，证券代码 300373，相信在您的关怀支持下，我们一定能够实现让世界信赖中国半导体的愿景。

Yangzhou Yangjie Electronic Technology Co., Ltd. is one of the few outstanding IDM manufactures in China which integrates discrete semiconductor chip design and production, semiconductor component assembly and test as well as market sales&services. We have a wide range of products including discrete semiconductor chips, rectifiers,protection devices,small signal parts, mosfets, power modules and SiC diodes which offer one-stop solution to our customers.

Our products are widely used in power supply, home appliance,lighting, security, telecommunication, customer electronics, green energy, industrial and automatic control, automotive electronics and other fields.

We were listed in Shenzhen Stock Exchange Market in 23 january,2014 with stock code 300373.We believe that we could achieve our vision “let the world trust Chinese semiconductor” with your support.

揚杰发展历程

Our History

2000
成立
江苏扬杰电子有限公司

2006
设立桥堆二极管产线

2009
设立4寸芯片产线

2012
IPO成功过会
通过TS16949认证
设立功率模块产线

2013
设立4寸芯片第二条产线
大规模自动化设备取代手工
Philips认证

2014
“300373”成功登陆深交所
台湾办事处成立
通过Delta认证

2015
设立DFN QFN产线
美国分公司成立
韩国办事处成立

2016
设立6寸
SKY芯片产线
成立
低压MOS研发中心

2017
设立
小信号产线

2018
设立汽车电子产线
收购宜兴杰芯高压MOS产线，
持有51%股份

2019
日本办事处成立

01 02 03 04 05 06 07 08 09 10 11

01 产品大类 Product Type

功率模块 Power modules

- 整流模块 Rectifier Power Modules
  IF: 30A~250A
  VBR: 800V~2000V
- 晶闸管模块 Thyristor Power Modules
  IF: 25A~200A
  VBR: 800V~2200V
- 快恢复模块Fast Recovery Power Modules
  IF: 100A~500A
  VBR: 400V~1200V
- 肖特基模块Schottky Power Modules
  IF: 200A~800A
  VBR: 100V~200V
- IGBT模块 IGBT Power Modules
  IC: 15A~400A
  VCES: 1350V

02 产品特点 Product Features

- **a** 自主晶圆设计能力及规模化制造能力保证稳定供货
  Wafer design and production back-up to ensure stable and cost effective supply
- **b** 更优的浪涌电流能力以及雪崩能力
  Higher surge current and avalanche capability
- **c** 更低的通态压降以及漏电流，降低开关损耗
  Lower VF and IR capability to reduce switching power dissipation
- **d** 更低的热阻设计
  Lower thermal resistance design
- **e** 良好的高温特性以及更低的应力设计
  High temperature durability and stress resistance design
- **f** 绝缘型以及非绝缘型模块封装，适合多领域应用
  Insulation and non-insulation module packages suitbable for different application

03 产品应用 Product Application

◆整流模块Rectifier Power Modules
工业变频器 Industrial Converters
电焊机 Welding Machines
不间断电源 UPS
直流电机电源 DC-DC Motors

◆晶闸管模块 Thyristor Power Modules
电机控制与驱动 Motor Control and Driver
电池充电 Battery Charger
加热器控制 Heating Controllers
静态开关电源 Static SMPS
不间断电源 UPS

◆快恢复和肖特基模块Fast Recovery and Schottky Power Modules
电焊机 Welding Machines
电镀电源 Plating Power Supplies
功率因数调整 PFC
直流电机供电线路 DC-DC Motors

◆IGBT模块 IGBT Power Modules
工业变频器 Industrial Converters
光伏逆变器 Solar Inverters
伺服电机 Server Motors
感应加热 Induction Heaters
工业焊机 Industrial Welding Machines

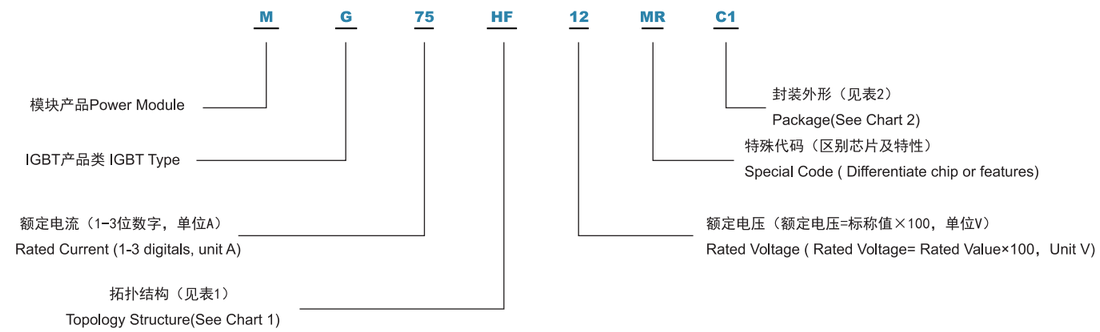
04 我们的客户 Our Client

中国中车 CRRC
invt 英威腾
INOVANCE
Midea
ESTUN AUTOMATION
山东奥太电气有限公司 AOTAI
DELIXI
MEGMEET
富士电机 Fuji Electric
华远焊机 HUAYUAN WELDER
KELONG 科华技术
动力源
DAIHEN OTC
EURA 欧瑞传动 EURA DRIVES
VEICHI
希望森兰
FGI 新风光
STEP 新时达
SUNGROW 阳光电源
INJET 英杰电气

CATALOG
目 录

产品命名规则 PRODUCT NAME RULE

IGBT产品型号组成 IGBT NAME RULE



整流桥、晶闸管、肖特基和快恢复产品型号组成 RECTIFIER/ THYRISTOR/SCHOTTKY/FRD POWER MODULE NAME RULE

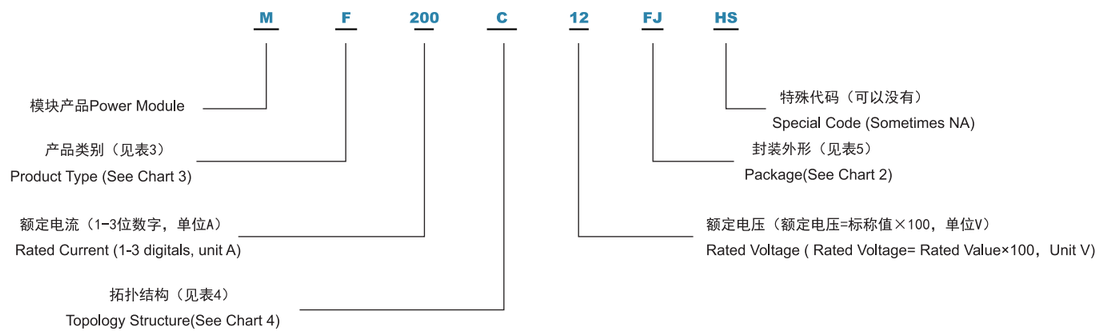


表1 Chart 1

外型代码Package Code	HF	ZU	ZD	U	UZ
拓扑结构Topology Structure	半桥 Half Bridge	一单元升压型One Unit Boost Type	一单元降压型One Unit Step Down	含续流单管 Include FWD	不含续流单管Non- FWD
产品类别Product Type	IGBT、Mosfet	IGBT、Mosfet	IGBT、Mosfet	IGBT	IGBT
代码Code	TF	P	TL	TT	/
拓扑结构Topology Structure	六单元	全桥整流+三相全桥+制动	一字型三电平	T字型三电平	/
产品类别Product Type	IGBT	IGBT	IGBT	IGBT	/

表2 Chart 2

外型代码Package Code	C1	C2	GJ	PM1	/
封装尺寸Package Size	94*34*30mm	108*62*30mm	30*28*12.8mm	55*31*15.5mm	/
外型代码Package Code	P3	E1/E1A	E2/E2A	E3	/
封装尺寸Package Size	62.6*56.8*16.8	107.5*45*20.5	122.5*62.5*20.5	152*62*20.8	/

表3 Chart 3

外型代码Package Code	D	F	T	B	M
产品类别Product Type	整流二极管 Rectifier Diode	快恢复二极管Fast Diode	晶闸管Thyristor	肖特基二极管Schottky Diode	Mosfet

表4 Chart 4

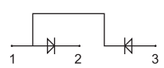
外型代码Package Code	C	A	K	S	H
拓扑结构Topology Structure	串联Series Connection	共阳Common Anode	共阴Common Cathode	三项整流Three Phase Rectifier	全桥Full Bridge
产品类别Product Type	D\F\T\B	D\F\T\B	D\F\T\B	D	D\F
代码Code	DU	U	SU	CB	DT
拓扑结构Topology Structure	双单管Double/Single	单管Single	6个单管 6 Single	半控-12单元为Half Control-12units SCR	6+1混合封装 6+1 Mixed
产品类别Product Type	D\F\T\B	D\F\T\B	T	T	T

表5 Chart 5

外型代码Package Code	D1/T1/F1	D2/F2/T2	D1N	L1	L2
封装尺寸Package Size	93*21*30mm	94*34*30mm	94*26*30mm	94*50*22mm	108*62*27mm
外型代码Package Code	M1	M2	M3	M4	M5
封装尺寸Package Size	60*32*27.3mm	72*42*30mm	94*54*30mm	82*42*22mm	94*54*17mm
外型代码Package Code	M1N	NM2	NM3	M7	M8
封装尺寸Package Size	60*32*20.8mm	72*42*39.7mm	94*54*39.7mm	70*40*34.5mm	80*40*37.5mm
外型代码Package Code	F3	F4N	F5	F6	FJ
封装尺寸Package Size	92*27*17mm	94*20*17mm	94*26*17mm	80*42*23mm	30*28*12.8mm
外型代码Package Code	FD	P1			
封装尺寸Package Size	108*62*30mm	55*31*15.5mm			

整流二极管模块
RECTIFIER DIODE MODULES

绝缘耐压：3000V(交流)
Viso:3000V(AC)

型 号 Part NO.	反向重复峰值电压 V_{RRM} (V)	正向平均电流 $I_{F(AV)}@T_C$		浪涌电流 I_{FSM} 10ms (A)	反向重复峰值电流 I_{RRM} 150℃ (mA)	最大正向压降 $V_{FM}@I_F$		结-壳热阻 $R_{th(j-c)}$ (℃/W)	封 装 Package	电路结构 Circuit structure
		(A)	(℃)			(V)	(A)			
MD36C08D1	800	36	104	650	5	1.40	100	0.5	D1	
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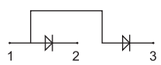
MD36C16D1	1600	36	104	650	5	1.40	100	0.5	D1	
MD36C18D1	1800	36	104	650	5	1.40	100	0.5	D1	
MD36A08D1	800	36	104	650	5	1.40	100	0.5	D1	
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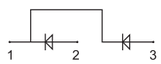
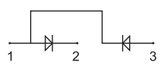
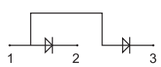
MD36A16D1	1600	36	104	650	5	1.40	100	0.5	D1	
MD36A18D1	1800	36	104	650	5	1.40	100	0.5	D1	
MD36K08D1	800	36	104	650	5	1.40	100	0.5	D1	
MD36K12D1	1200	36	104	650	5	1.40	100	0.5	D1	
MD36K16D1	1600	36	104	650	5	1.40	100	0.5	D1	
MD36K18D1	1800	36	104	650	5	1.40	100	0.5	D1	
MD60C08D1	800	60	100	1150	5	1.45	200	0.295	D1	
MD60C12D1	1200	60	100	1150	5	1.45	200	0.295	D1	
MD60C16D1	1600	60	100	1150	5	1.45	200	0.295	D1	
MD60C18D1	1800	60	100	1150	5	1.45	200	0.295	D1	
MD60A08D1	800	60	100	1150	5	1.45	200	0.295	D1	
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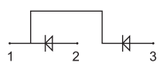
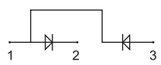
MD60A16D1	1600	60	100	1150	5	1.45	200	0.295	D1	
MD60A18D1	1800	60	100	1150	5	1.45	200	0.295	D1	
MD60K08D1	800	60	100	1150	5	1.45	200	0.295	D1	
MD60K12D1	1200	60	100	1150	5	1.45	200	0.295	D1	
MD60K16D1	1600	60	100	1150	5	1.45	200	0.295	D1	
MD60K18D1	1800	60	100	1150	5	1.45	200	0.295	D1	
MD70C08D1	800	70	102	1400	5	1.30	200	0.255	D1	
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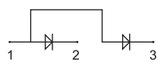
MD70C16D1	1600	70	102	1400	5	1.30	200	0.255	D1	
MD70C18D1	1800	70	102	1400	5	1.30	200	0.255	D1	
MD70A08D1	800	70	102	1400	5	1.30	200	0.255	D1	
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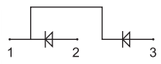
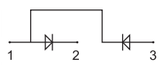
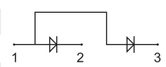
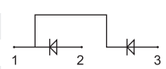
MD70A16D1	1600	70	102	1400	5	1.30	200	0.255	D1	
MD70A18D1	1800	70	102	1400	5	1.30	200	0.255	D1	
MD70K08D1	800	70	102	1400	5	1.30	200	0.255	D1	
MD70K12D1	1200	70	102	1400	5	1.30	200	0.255	D1	
MD70K16D1	1600	70	102	1400	5	1.30	200	0.255	D1	
MD70K18D1	1800	70	102	1400	5	1.30	200	0.255	D1	
MD100C08D1	800	100	109	2500	5	1.40	300	0.175	D1	
MD100C12D1	1200	100	109	2500	5	1.40	300	0.175	D1	
MD100C16D1	1600	100	109	2500	5	1.40	300	0.175	D1	
MD100C18D1	1800	100	109	2500	5	1.40	300	0.175	D1	

D1

整流二极管模块
RECTIFIER DIODE MODULES

绝缘耐压：3000V(交流)
Viso:3000V(AC)

型 号 Part NO.	反向重复峰值电压 V_{RRM} (V)	正向平均电流 $I_{F(AV)}@T_C$ (A)	(℃)	浪涌电流 I_{FSM} 10ms (A)	反向重复峰值电流 I_{RRM} 150℃ (mA)	最大正向压降 $V_{FM}@I_F$ (V)	(A)	结-壳热阻 R_{thj-c} (℃/W)	封 装 Package	电路结构 Circuit structure
MD100A08D1	800	100	109	2500	5	1.40	300	0.175	D1	
MD100A12D1	1200	100	109	2500	5	1.40	300	0.175	D1	
MD100A16D1	1600	100	109	2500	5	1.40	300	0.175	D1	
MD100A18D1	1800	100	109	2500	5	1.40	300	0.175	D1	
MD100K08D1	800	100	109	2500	5	1.40	300	0.175	D1	
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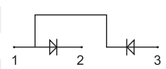
MD100K16D1	1600	100	109	2500	5	1.40	300	0.175	D1	
MD100K18D1	1800	100	109	2500	5	1.40	300	0.175	D1	
MD120C08D1	800	120	106	2800	6	1.35	300	0.13	D1	
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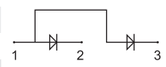
MD120C16D1	1600	120	106	2800	6	1.35	300	0.13	D1	
MD120C18D1	1800	120	106	2800	6	1.35	300	0.13	D1	
MD120A08D1	800	120	106	2800	6	1.35	300	0.13	D1	
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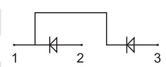
MD120A16D1	1600	120	106	2800	6	1.35	300	0.13	D1	
MD120A18D1	1800	120	106	2800	6	1.35	300	0.13	D1	
MD120K08D1	800	120	106	2800	6	1.35	300	0.13	D1	
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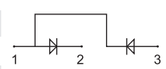
MD120K16D1	1600	120	106	2800	6	1.35	300	0.13	D1	
MD120K18D1	1800	120	106	2800	6	1.35	300	0.13	D1	
MD55C08D1	800	55	100	1150	5	1.45	200	0.295	D1	
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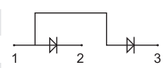
MD55C16D1	1600	55	100	1150	5	1.45	200	0.295	D1	
MD55C18D1	1800	55	100	1150	5	1.45	200	0.295	D1	
MD55A08D1	800	55	100	1150	5	1.45	200	0.295	D1	
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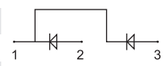
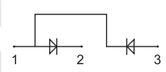
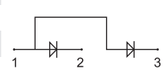
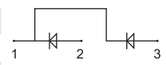
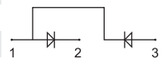
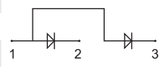
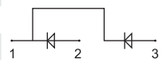
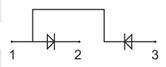
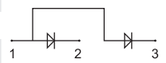
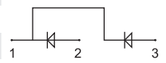
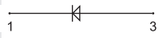
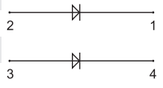
MD55A16D1	1600	55	100	1150	5	1.45	200	0.295	D1	
MD55A18D1	1800	55	100	1150	5	1.45	200	0.295	D1	
MD55K08D1	800	55	100	1150	5	1.45	200	0.295	D1	
MD55K12D1	1200	55	100	1150	5	1.45	200	0.295	D1	
MD55K16D1	1600	55	100	1150	5	1.45	200	0.295	D1	
MD55K18D1	1800	55	100	1150	5	1.45	200	0.295	D1	
MD165C08D2	800	165	101	6000	9	1.40	300	0.105	D2	
MD165C12D2	1200	165	101	6000	9	1.40	300	0.105	D2	
MD165C16D2	1600	165	101	6000	9	1.40	300	0.105	D2	
MD165C18D2	1800	165	101	6000	9	1.40	300	0.105	D2	
MD165C20D2	2000	165	101	6000	9	1.4	300	0.105	D2	
MD165A08D2	800	165	101	6000	9	1.40	300	0.105	D2	
MD165A12D2	1200	165	101	6000	9	1.40	300	0.105	D2	
MD165A16D2	1600	165	101	6000	9	1.40	300	0.105	D2	
MD165A18D2	1800	165	101	6000	9	1.40	300	0.105	D2	
MD165A20D2	2000	165	101	6000	9	1.4	300	0.105	D2	

D1

D2

整流二极管模块
RECTIFIER DIODE MODULES

绝缘耐压：3000V(交流)
Viso:3000V(AC)

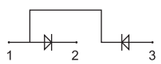
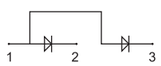
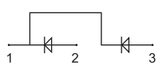
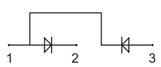
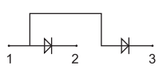
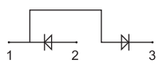
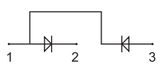
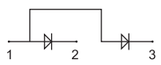
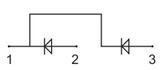
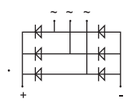
型 号 Part NO.	反向重复峰值电压 V_{RRM} (V)	正向平均电流 $I_{F(AV)}@T_C$ (A)	(℃)	浪涌电流 I_{FSM} 10ms (A)	反向重复峰值电流 I_{RRM} 150℃ (mA)	最大正向压降 $V_{FM}@I_F$ (V)	(A)	结-壳热阻 $R_{th(j-c)}$ (℃/W)	封 装 Package	电路结构 Circuit structure
MD165K08D2	800	165	101	6000	9	1.40	300	0.105	D2	
MD165K12D2	1200	165	101	6000	9	1.40	300	0.105	D2	
MD165K16D2	1600	165	101	6000	9	1.40	300	0.105	D2	
MD165K18D2	1800	165	101	6000	9	1.40	300	0.105	D2	
MD165K20D2	2000	165	101	6000	9	1.4	300	0.105	D2	
MD200C08D2	800	200	95	6800	9	1.30	300	0.09	D2	
MD200C12D2	1200	200	95	6800	9	1.30	300	0.09	D2	
MD200C16D2	1600	200	95	6800	9	1.30	300	0.09	D2	
MD200C18D2	1800	200	95	6800	9	1.30	300	0.09	D2	
MD200A08D2	800	200	95	6800	9	1.30	300	0.09	D2	
MD200A12D2	1200	200	95	6800	9	1.30	300	0.09	D2	
MD200A16D2	1600	200	95	6800	9	1.30	300	0.09	D2	
MD200A18D2	1800	200	95	6800	9	1.30	300	0.09	D2	
MD200K08D2	800	200	95	6800	9	1.30	300	0.09	D2	
MD200K12D2	1200	200	95	6800	9	1.30	300	0.09	D2	
MD200K16D2	1600	200	95	6800	9	1.30	300	0.09	D2	
MD200K18D2	1800	200	95	6800	9	1.30	300	0.09	D2	
MD240C08D2	800	240	95	7550	9	1.25	300	0.08	D2	
MD240C12D2	1200	240	95	7550	9	1.25	300	0.08	D2	
MD240C16D2	1600	240	95	7550	9	1.25	300	0.08	D2	
MD240C18D2	1800	240	95	7550	9	1.25	300	0.08	D2	
MD240A08D2	800	240	95	7550	9	1.25	300	0.08	D2	
MD240A12D2	1200	240	95	7550	9	1.25	300	0.08	D2	
MD240A16D2	1600	240	95	7550	9	1.25	300	0.08	D2	
MD240A18D2	1800	240	95	7550	9	1.25	300	0.08	D2	
MD240K08D2	800	240	95	7550	9	1.25	300	0.08	D2	
MD240K12D2	1200	240	95	7550	9	1.25	300	0.08	D2	
MD240K16D2	1600	240	95	7550	9	1.25	300	0.08	D2	
MD240K18D2	1800	240	95	7550	9	1.25	300	0.08	D2	
MD165U08D2	800	165	101	6000	9	1.2	300	0.21	D2	
MD165U12D2	1200	165	101	6000	9	1.2	300	0.21	D2	
MD165U16D2	1600	165	101	6000	9	1.2	300	0.21	D2	
MD165U18D2	1800	165	101	6000	9	1.2	300	0.21	D2	
MD200U08D2	800	200	95	6800	9	1.3	300	0.18	D2	
MD200U12D2	1200	200	95	6800	9	1.3	300	0.18	D2	
MD200U16D2	1600	200	95	6800	9	1.3	300	0.18	D2	
MD200U18D2	1800	200	95	6800	9	1.3	300	0.18	D2	
MD30DU08DA	800	30	104	650	5	1.25	100	0.5	DA	
MD30DU12DA	1200	30	104	650	5	1.25	100	0.5	DA	
MD30DU16DA	1600	30	104	650	5	1.25	100	0.5	DA	
MD30DU18DA	1800	30	104	650	5	1.25	100	0.5	DA	

D2

DA

整流二极管模块
RECTIFIER DIODE MODULES

绝缘耐压：3000V(交流)
Viso:3000V(AC)

型 号 Part NO.	反向重复峰值电压 V_{RRM} (V)	正向平均电流 $I_{F(AV)}$@Tc		浪涌电流 I_{FSM} 10ms (A)	反向重复峰值电流 I_{RRM} 150℃ (mA)	最大正向压降 V_{FM}@I_F		结-壳热阻 R_{thj-c} (℃/W)	封 装 Package	电路结构 Circuit structure
		(A)	(℃)			(V)	(A)			
MD60C08D1N	800	60	100	1150	5	1.45	200	0.15	D1N	
MD60C12D1N	1200	60	100	1150	5	1.45	200	0.15	D1N	
MD60C16D1N	1600	60	100	1150	5	1.45	200	0.15	D1N	
MD60C18D1N	1800	60	100	1150	5	1.45	200	0.15	D1N	
MD60A08D1N	800	60	100	1150	5	1.45	200	0.15	D1N	
MD60A12D1N	1200	60	100	1150	5	1.45	200	0.15	D1N	
MD60A16D1N	1600	60	100	1150	5	1.45	200	0.15	D1N	
MD60A18D1N	1800	60	100	1150	5	1.45	200	0.15	D1N	
MD60K08D1N	800	60	100	1150	5	1.45	200	0.15	D1N	
MD60K12D1N	1200	60	100	1150	5	1.45	200	0.15	D1N	
MD60K16D1N	1600	60	100	1150	5	1.45	200	0.15	D1N	
MD60K18D1N	1800	60	100	1150	5	1.45	200	0.15	D1N	
MD100C08D1N	800	100	106	2800	6	1.35	300	0.13	D1N	
MD100C12D1N	1200	100	106	2800	6	1.35	300	0.13	D1N	
MD100C16D1N	1600	100	106	2800	6	1.35	300	0.13	D1N	
MD100C18D1N	1800	100	106	2800	6	1.35	300	0.13	D1N	
MD100A08D1N	800	100	106	2800	6	1.35	300	0.13	D1N	
MD100A12D1N	1200	100	106	2800	6	1.35	300	0.13	D1N	
MD100A16D1N	1600	100	106	2800	6	1.35	300	0.13	D1N	
MD100A18D1N	1800	100	106	2800	6	1.35	300	0.13	D1N	
MD100K08D1N	800	100	106	2800	6	1.35	300	0.13	D1N	
MD100K12D1N	1200	100	106	2800	6	1.35	300	0.13	D1N	
MD100K16D1N	1600	100	106	2800	6	1.35	300	0.13	D1N	
MD100K18D1N	1800	100	106	2800	6	1.35	300	0.13	D1N	
MD120C08D1N	800	120	106	2800	6	1.35	300	0.13	D1N	
MD120C12D1N	1200	120	106	2800	6	1.35	300	0.13	D1N	
MD120C16D1N	1600	120	106	2800	6	1.35	300	0.13	D1N	
MD120C18D1N	1800	120	106	2800	6	1.35	300	0.13	D1N	
MD120A08D1N	800	120	106	2800	6	1.35	300	0.13	D1N	
MD120A12D1N	1200	120	106	2800	6	1.35	300	0.13	D1N	
MD120A16D1N	1600	120	106	2800	6	1.35	300	0.13	D1N	
MD120A18D1N	1800	120	106	2800	6	1.35	300	0.13	D1N	
MD120K08D1N	800	120	106	2800	6	1.35	300	0.13	D1N	
MD120K12D1N	1200	120	106	2800	6	1.35	300	0.13	D1N	
MD120K16D1N	1600	120	106	2800	6	1.35	300	0.13	D1N	
MD120K18D1N	1800	120	106	2800	6	1.35	300	0.13	D1N	
MD50S08M1	800	50	96	460	3	1.50	150	0.25	M1	
MD50S12M1	1200	50	96	460	3	1.50	150	0.25	M1	
MD50S16M1	1600	50	96	460	3	1.50	150	0.25	M1	
MD50S18M1	1800	50	96	460	3	1.50	150	0.25	M1	
MD60S08M2	800	60	110	460	5	1.80	150	0.242	M2	

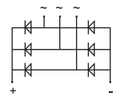
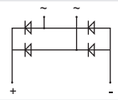
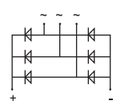

D1N


M1


M2

整流二极管模块
RECTIFIER DIODE MODULES

绝缘耐压：3000V(交流)
Viso:3000V(AC)

型 号 Part NO.	反向重复峰值电压 V_{RRM} (V)	正向平均电流 $I_{F(AV)}$@Tc		浪涌电流 I_{FSM} 10ms (A)	反向重复峰值电流 I_{RRM} 150℃ (mA)	最大正向压降 V_{FM}@I_F		结-壳热阻 R_{thj-c} (℃/W)	封 装 Package	电路结构 Circuit structure
		(A)	(℃)			(V)	(A)			
MD60S12M2	1200	60	110	460	5	1.80	150	0.242	M2	
MD60S16M2	1600	60	110	460	5	1.80	150	0.242	M2	
MD60S18M2	1800	60	110	460	5	1.80	150	0.242	M2	
MD75S08M2	800	75	110	750	5	1.60	150	0.183	M2	
MD75S12M2	1200	75	110	750	5	1.60	150	0.183	M2	
MD75S16M2	1600	75	110	750	5	1.60	150	0.183	M2	
MD75S18M2	1800	75	110	750	5	1.60	150	0.183	M2	
MD100S08M2	800	100	100	750	5	1.90	150	0.167	M2	
MD100S12M2	1200	100	100	750	5	1.90	150	0.167	M2	
MD100S16M2	1600	100	100	750	5	1.90	150	0.167	M2	
MD100S18M2	1800	100	100	750	5	1.90	150	0.167	M2	
MD60H08M2	800	60	100	750	5	1.90	150	0.25	M2	
MD60H12M2	1200	60	100	750	5	1.90	150	0.25	M2	
MD60H16M2	1600	60	100	750	5	1.90	150	0.25	M2	
MD60H18M2	1800	60	100	750	5	1.90	150	0.25	M2	
MD100S08M3	800	100	100	920	5	1.90	300	0.150	M3	
MD100S12M3	1200	100	100	920	5	1.90	300	0.150	M3	
MD100S16M3	1600	100	100	920	5	1.90	300	0.150	M3	
MD100S18M3	1800	100	100	920	5	1.90	300	0.150	M3	
MD130S08M3	800	130	100	1200	5	1.80	300	0.150	M3	
MD130S12M3	1200	130	100	1200	5	1.80	300	0.150	M3	
MD130S16M3	1600	130	100	1200	5	1.80	300	0.150	M3	
MD130S18M3	1800	130	100	1200	5	1.80	300	0.150	M3	
MD160S08M3	800	160	100	1800	6	1.75	300	0.108	M3	
MD160S12M3	1200	160	100	1800	6	1.75	300	0.108	M3	
MD160S16M3	1600	160	100	1800	6	1.75	300	0.108	M3	
MD160S18M3	1800	160	100	1800	6	1.75	300	0.108	M3	
MD200S08M3	800	200	100	2240	6	1.70	300	0.075	M3	
MD200S12M3	1200	200	100	2240	6	1.70	300	0.075	M3	
MD200S16M3	1600	200	100	2240	6	1.70	300	0.075	M3	
MD200S18M3	1800	200	100	2240	6	1.70	300	0.075	M3	
MD250S08M3	800	250	100	2500	6	1.60	300	0.06	M3	
MD250S12M3	1200	250	100	2500	6	1.60	300	0.06	M3	
MD250S16M3	1600	250	100	2500	6	1.60	300	0.06	M3	
MD250S18M3	1800	250	100	2500	6	1.60	300	0.06	M3	
MD50S08M4	800	50	110	460	5	1.7	150	0.242	M4	
MD50S12M4	1200	50	110	460	5	1.7	150	0.242	M4	
MD50S16M4	1600	50	110	460	5	1.7	150	0.242	M4	
MD50S18M4	1800	50	110	460	5	1.7	150	0.242	M4	
MD75S08M4	800	75	110	750	5	1.5	150	0.183	M4	
MD75S12M4	1200	75	110	750	5	1.5	150	0.183	M4	
MD75S16M4	1600	75	110	750	5	1.5	150	0.183	M4	


M2

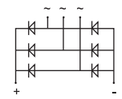

M3


M4

整流二极管模块
RECTIFIER DIODE MODULES

绝缘耐压：3000V(交流)
V_{ISO}:3000V(AC)

型 号 Part NO.	反向重复峰值电压 V_{RRM} (V)	正向平均电流 $I_{F(AV)}$@Tc		浪涌电流 I_{FSM} 10ms (A)	反向重复峰值电流 I_{RRM} 150℃ (mA)	最大正向压降 V_{FM}@I_F		结-壳热阻 R_{thj-c} (℃/W)	封 装 Package	电路结构 Circuit structure
		(A)	(℃)			(V)	(A)			
MD75S18M4	1800	75	110	750	5	1.5	150	0.183	M4	
MD100S08M4	800	100	100	920	5	1.90	300	0.167	M4	
MD100S12M4	1200	100	100	920	5	1.90	300	0.167	M4	
MD100S16M4	1600	100	100	920	5	1.90	300	0.167	M4	
MD100S18M4	1800	100	100	920	5	1.90	300	0.167	M4	
MD100S08M5	800	100	100	920	5	1.90	300	0.15	M5	
MD100S12M5	1200	100	100	920	5	1.90	300	0.15	M5	
MD100S16M5	1600	100	100	920	5	1.90	300	0.15	M5	
MD100S18M5	1800	100	100	920	5	1.90	300	0.15	M5	
MD130S08M5	800	130	100	1200	5	1.80	300	0.15	M5	
MD130S12M5	1200	130	100	1200	5	1.80	300	0.15	M5	
MD130S16M5	1600	130	100	1200	5	1.80	300	0.15	M5	
MD130S18M5	1800	130	100	1200	5	1.80	300	0.15	M5	
MD160S08M5	800	160	100	1800	6	1.75	300	0.108	M5	
MD160S12M5	1200	160	100	1800	6	1.75	300	0.108	M5	
MD160S16M5	1600	160	100	1800	6	1.75	300	0.108	M5	
MD160S18M5	1800	160	100	1800	6	1.75	300	0.108	M5	
MD200S08M5	800	200	100	2240	6	1.70	300	0.075	M5	
MD200S12M5	1200	200	100	2240	6	1.70	300	0.075	M5	
MD200S16M5	1600	200	100	2240	6	1.70	300	0.075	M5	
MD200S18M5	1800	200	100	2240	6	1.70	300	0.075	M5	
MD250S08M5	800	250	100	2500	6	1.60	300	0.06	M5	
MD250S12M5	1200	250	100	2500	6	1.60	300	0.06	M5	
MD250S16M5	1600	250	100	2500	6	1.60	300	0.06	M5	
MD250S18M5	1800	250	100	2500	6	1.60	300	0.06	M5	
MD60S08NM2	800	60	110	460	5	1.80	150	0.242	NM2	
MD60S12NM2	1200	60	110	460	5	1.80	150	0.242	NM2	
MD60S16NM2	1600	60	110	460	5	1.80	150	0.242	NM2	
MD60S18NM2	1800	60	110	460	5	1.80	150	0.242	NM2	
MD75S08NM2	800	75	110	750	5	1.60	150	0.183	NM2	
MD75S12NM2	1200	75	110	750	5	1.60	150	0.183	NM2	
MD75S16NM2	1600	75	110	750	5	1.60	150	0.183	NM2	
MD75S18NM2	1800	75	110	750	5	1.60	150	0.183	NM2	
MD100S08NM2	800	100	100	750	5	1.90	150	0.167	NM2	
MD100S12NM2	1200	100	100	750	5	1.90	150	0.167	NM2	
MD100S16NM2	1600	100	100	750	5	1.90	150	0.167	NM2	
MD100S18NM2	1800	100	100	750	5	1.90	150	0.167	NM2	
MD100S08NM3	800	100	100	920	5	1.90	300	0.15	NM3	
MD100S12NM3	1200	100	100	920	5	1.90	300	0.15	NM3	
MD100S16NM3	1600	100	100	920	5	1.90	300	0.15	NM3	
MD100S18NM3	1800	100	100	920	5	1.90	300	0.15	NM3	
MD160S08NM3	800	160	100	1800	6	1.75	300	0.108	NM3	




M4


M5

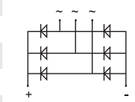

NM2

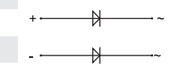

NM3

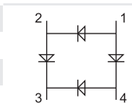
整流二极管模块
RECTIFIER DIODE MODULES

绝缘耐压：3000V(交流)
V_{ISO}:3000V(AC)

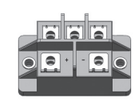
型 号 Part NO.	反向重复峰值电压 V_{RRM} (V)	正向平均电流 $I_{F(AV)}$@Tc		浪涌电流 I_{FSM} 10ms (A)	反向重复峰值电流 I_{RRM} 150℃ (mA)	最大正向压降 V_{FM}@I_F		结-壳热阻 R_{thj-c} (℃/W)	封 装 Package	电路结构 Circuit structure
		(A)	(℃)			(V)	(A)			
MD160S12NM3	1200	160	100	1800	6	1.75	300	0.108	NM3	
MD160S16NM3	1600	160	100	1800	6	1.75	300	0.108	NM3	
MD160S18NM3	1800	160	100	1800	6	1.75	300	0.108	NM3	
MD250S08NM3	800	250	100	2500	6	1.60	300	0.06	NM3	
MD250S12NM3	1200	250	100	2500	6	1.60	300	0.06	NM3	
MD250S16NM3	1600	250	100	2500	6	1.60	300	0.06	NM3	
MD250S18NM3	1800	250	100	2500	6	1.60	300	0.06	NM3	
MD60S08M7	800	60	110	750	5	1.60	150	0.183	M7	
MD60S12M7	1200	60	110	750	5	1.60	150	0.183	M7	
MD60S16M7	1600	60	110	750	5	1.60	150	0.183	M7	
MD60S18M7	1800	60	110	750	5	1.60	150	0.183	M7	
MD75S08M8	800	75	110	750	5	1.60	150	0.18	M8	
MD75S12M8	1200	75	110	750	5	1.60	150	0.18	M8	
MD75S16M8	1600	75	110	750	5	1.60	150	0.18	M8	
MD75S18M8	1800	75	110	750	5	1.60	150	0.18	M8	
MD100S08M8	800	100	100	920	5	1.90	300	0.15	M8	
MD100S12M8	1200	100	100	920	5	1.90	300	0.15	M8	
MD100S16M8	1600	100	100	920	5	1.90	300	0.15	M8	
MD100S18M8	1800	100	100	920	5	1.90	300	0.15	M8	
MD60DU08M7	800	60	100	1150	5	1.05	60	0.18	M7	
MD60DU12M7	1200	60	100	1150	5	1.05	60	0.18	M7	
MD60DU16M7	1600	60	100	1150	5	1.05	60	0.18	M7	
MD60DU18M7	1800	60	100	1150	5	1.05	60	0.18	M7	
MD50H08FJ	800	50	104	650	1	1.40	100	0.15	FJ	
MD50H12FJ	1200	50	104	650	1	1.40	100	0.15	FJ	
MD50H16FJ	1600	50	104	650	1	1.40	100	0.15	FJ	
MD50H18FJ	1800	50	104	650	1	1.40	100	0.15	FJ	








NM3

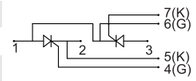
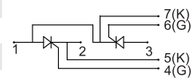
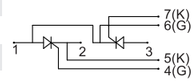
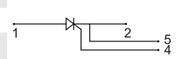

M7


M8


FJ

晶闸管模块
THYRISTOR MODULES

绝缘耐压：3000V(交流) 电压临界上升率：大于1000V/us
Viso:3000V(AC) dv/dt:1000 V/us

型 号 Part NO.	正向重复峰值电压/反向重复峰值电压 V_{DRM}/V_{RRM} (V)	通态平均电流 I_{TAV}@Tc=85°C (A)	通态浪涌电流 I_{TSM} 10ms (A)	正向重复峰值电流/反向重复峰值电流 I_{DRM}/I_{RRM} 125°C (mA)	通态压降@通态电流 V_{TM} @ I_T (V)	(A)	触发电流 I_{GT} (mA)	触发电压 V_{GT} (V)	结-壳热阻 R_{thj-c} (℃/W)	封 装 Package	电路结构 Circuit structure
MT25C08T1	800	25	550	10	1.80	75	150	2.5	0.45	T1	
MT25C12T1	1200	25	550	10	1.80	75	150	2.5	0.45	T1	
MT25C16T1	1600	25	550	10	1.80	75	150	2.5	0.45	T1	
MT25C18T1	1800	25	550	10	1.80	75	150	2.5	0.45	T1	
MT40C08T1	800	40	1000	15	1.95	200	150	2.5	0.33	T1	
MT40C12T1	1200	40	1000	15	1.95	200	150	2.5	0.33	T1	
MT40C16T1	1600	40	1000	15	1.95	200	150	2.5	0.33	T1	
MT40C18T1	1800	40	1000	15	1.95	200	150	2.5	0.33	T1	
MT60C08T1	800	60	1500	15	1.65	200	150	3.0	0.29	T1	
MT60C12T1	1200	60	1500	15	1.65	200	150	3.0	0.29	T1	
MT60C16T1	1600	60	1500	15	1.65	200	150	3.0	0.29	T1	
MT60C18T1	1800	60	1500	15	1.65	200	150	3.0	0.29	T1	
MT90C08T1	800	90	2000	20	1.65	300	150	3.0	0.14	T1	
MT90C12T1	1200	90	2000	20	1.65	300	150	3.0	0.14	T1	
MT90C16T1	1600	90	2000	20	1.65	300	150	3.0	0.14	T1	
MT90C18T1	1800	90	2000	20	1.65	300	150	3.0	0.14	T1	
MT110C08T1	800	110	2250	20	1.65	300	150	3.0	0.14	T1	
MT110C12T1	1200	110	2250	20	1.65	300	150	3.0	0.14	T1	
MT110C16T1	1600	110	2250	20	1.65	300	150	3.0	0.14	T1	
MT110C18T1	1800	110	2250	20	1.65	300	150	3.0	0.14	T1	
MT90C22T1	2200	90	2000	20	1.65	300	150	3.0	0.14	T1	
MT90C08T1D	800	90	2000	20	1.65	300	150	3.0	0.14	T1D	
MT90C12T1D	1200	90	2000	20	1.65	300	150	3.0	0.14	T1D	
MT90C16T1D	1600	90	2000	20	1.65	300	150	3.0	0.14	T1D	
MT90C18T1D	1800	90	2000	20	1.65	300	150	3.0	0.14	T1D	
MT130C08T2	800	130	4700	40	1.80	500	150	3.0	0.09	T2	
MT130C12T2	1200	130	4700	40	1.80	500	150	3.0	0.09	T2	
MT130C16T2	1600	130	4700	40	1.80	500	150	3.0	0.09	T2	
MT130C18T2	1800	130	4700	40	1.80	500	150	3.0	0.09	T2	
MT160C08T2	800	160	5400	40	1.75	500	150	3.0	0.085	T2	
MT160C12T2	1200	160	5400	40	1.75	500	150	3.0	0.085	T2	
MT160C16T2	1600	160	5400	40	1.75	500	150	3.0	0.085	T2	
MT160C18T2	1800	160	5400	40	1.75	500	150	3.0	0.085	T2	
MT200C08T2	800	200	5500	50	1.68	500	200	3.0	0.08	T2	
MT200C12T2	1200	200	5500	50	1.68	500	200	3.0	0.08	T2	
MT200C16T2	1600	200	5500	50	1.68	500	200	3.0	0.08	T2	
MT200C18T2	1800	200	5500	50	1.68	500	200	3.0	0.08	T2	
MT200U08T2	800	200	5500	50	1.68	500	200	3.0	0.16	T2	
MT200U12T2	1200	200	5500	50	1.68	500	200	3.0	0.16	T2	
MT200U16T2	1600	200	5500	50	1.68	500	200	3.0	0.16	T2	
MT200U18T2	1800	200	5500	50	1.68	500	200	3.0	0.16	T2	

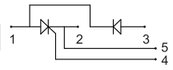

T1


T1D


T2

晶闸管/整流二极管模块
THYRISTOR / RECTIFIER DIODE MODULES

绝缘耐压：3000V(交流) 电压临界上升率：大于1000V/us
Viso:3000V(AC) dv/dt:1000 V/us

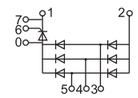
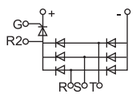
型 号 Part NO.	正向重复峰值电压/反向重复峰值电压 V_{DRM}/V_{RRM} (V)	通态平均电流 I_{TAV}@Tc=85°C (A)	通态浪涌电流 I_{TSM} 10ms (A)	通态压降@通态电流 V_{TM} @ I_T (V)	(A)	二极管 Diode 反向重复峰值电流 I_{RRM} 150°C (mA)	结-壳热阻 R_{thj-c} (℃/W)	晶闸管 Thyristor 触发电流 I_{GT} (mA)	触发电压 V_{GT} (V)	正向重复峰值电流/反向重复峰值电流 I_{DRM}/I_{RRM} 125°C (mA)	结-壳热阻 R_{thj-c} (℃/W)	封 装 Package	电路结构 Circuit structure
MT25CB08T1	800	25	550	1.80	75	6	0.45	150	2.5	10	0.90	T1	
MT25CB12T1	1200	25	550	1.80	75	6	0.45	150	2.5	10	0.90	T1	
MT25CB16T1	1600	25	550	1.80	75	6	0.45	150	2.5	10	0.90	T1	
MT25CB18T1	1800	25	550	1.80	75	6	0.45	150	2.5	10	0.90	T1	
MT40CB08T1	800	40	1000	1.95	200	6	0.33	150	2.5	15	0.65	T1	
MT40CB12T1	1200	40	1000	1.95	200	6	0.33	150	2.5	15	0.65	T1	
MT40CB16T1	1600	40	1000	1.95	200	6	0.33	150	2.5	15	0.65	T1	
MT40CB18T1	1800	40	1000	1.95	200	6	0.33	150	2.5	15	0.65	T1	
MT60CB08T1	800	60	1500	1.65	200	6	0.29	150	3.0	15	0.57	T1	
MT60CB12T1	1200	60	1500	1.65	200	6	0.29	150	3.0	15	0.57	T1	
MT60CB16T1	1600	60	1500	1.65	200	6	0.29	150	3.0	15	0.57	T1	
MT60CB18T1	1800	60	1500	1.65	200	6	0.29	150	3.0	15	0.57	T1	
MT90CB08T1	800	90	2000	1.65	300	6	0.14	150	3.0	20	0.28	T1	
MT90CB12T1	1200	90	2000	1.65	300	6	0.14	150	3.0	20	0.28	T1	
MT90CB16T1	1600	90	2000	1.65	300	6	0.14	150	3.0	20	0.28	T1	
MT90CB18T1	1800	90	2000	1.65	300	6	0.14	150	3.0	20	0.28	T1	
MT110CB08T1	800	110	2250	1.65	300	6	0.14	150	3.0	20	0.28	T1	
MT110CB12T1	1200	110	2250	1.65	300	6	0.14	150	3.0	20	0.28	T1	
MT110CB16T1	1600	110	2250	1.65	300	6	0.14	150	3.0	20	0.28	T1	
MT110CB18T1	1800	110	2250	1.65	300	6	0.14	150	3.0	20	0.28	T1	
MT130CB08T2	800	130	4700	1.80	500	9	0.09	150	3.0	40	0.18	T2	
MT130CB12T2	1200	130	4700	1.80	500	9	0.09	150	3.0	40	0.18	T2	
MT130CB16T2	1600	130	4700	1.80	500	9	0.09	150	3.0	40	0.18	T2	
MT130CB18T2	1800	130	4700	1.80	500	9	0.09	150	3.0	40	0.18	T2	
MT160CB08T2	800	160	5400	1.70	500	9	0.085	150	3.0	40	0.17	T2	
MT160CB12T2	1200	160	5400	1.70	500	9	0.085	150	3.0	40	0.17	T2	
MT160CB16T2	1600	160	5400	1.70	500	9	0.085	150	3.0	40	0.17	T2	
MT160CB18T2	1800	160	5400	1.70	500	9	0.085	150	3.0	40	0.17	T2	
MT200CB08T2	800	200	6800	1.70	620	9	0.08	200	3.0	40	0.16	T2	
MT200CB12T2	1200	200	6800	1.70	620	9	0.08	200	3.0	40	0.16	T2	
MT200CB16T2	1600	200	6800	1.70	620	9	0.08	200	3.0	40	0.16	T2	
MT200CB18T2	1800	200	6800	1.70	620	9	0.08	200	3.0	40	0.16	T2	


T1


T2

晶闸管/三相整流桥模块
THYRISTOR /THREE PHASE RECTIFIER MODULES

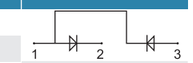
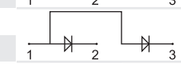
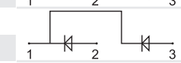
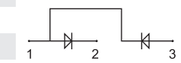
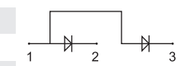
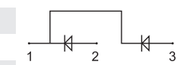
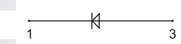
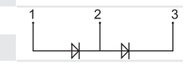
绝缘耐压：3000V(交流) 电压临界上升率：大于1000V/us
Viso:3000V(AC) dv/dt:1000 V/us

型 号 Part NO.	正向重复峰值电压/反向重复峰值电压 V_{DRM}/V_{RRM} (V)	通态平均电流 I_{TAV}@ T_C=85℃ (A)		通态浪涌电流 I_{TSM} 10ms (A)	二极管Diode 最大正向压降 V_{FM} @I_F		反向重复峰值电流 I_{RRM} 150℃ (mA)	结-壳热阻 R_{thj-c} (℃/W)	晶闸管Thyristor 触发电流 I_{GT} (mA)	触发电压 V_{GT} (V)	通态压降@通态电流 V_{TM}@I_T		正向重复峰值电流/反向重复峰值电流 I_{DRM} /I_{RRM} 125℃ (mA)	结-壳热阻 R_{thj-c} (℃/W)	封 装 Package	电路结构 Circuit structure
		(A)	(V)		(V)	(A)					(V)	(A)				
MT75DT08L1	800	75	99	920	1.4	100	6	0.20	150	3.0	1.30	100	20	0.3	L1	
MT75DT12L1	1200	75	99	920	1.4	100	6	0.20	150	3.0	1.30	100	20	0.3	L1	
MT75DT16L1	1600	75	99	920	1.4	100	6	0.20	150	3.0	1.30	100	20	0.3	L1	
MT75DT18L1	1800	75	99	920	1.4	100	6	0.20	150	3.0	1.30	100	20	0.3	L1	
MT100DT08L1	800	100	92	1200	1.35	100	6	0.18	150	3.0	1.25	100	20	0.26	L1	
MT100DT12L1	1200	100	92	1200	1.35	100	6	0.18	150	3.0	1.25	100	20	0.26	L1	
MT100DT16L1	1600	100	92	1200	1.35	100	6	0.18	150	3.0	1.25	100	20	0.26	L1	
MT100DT18L1	1800	100	92	1200	1.35	100	6	0.18	150	3.0	1.25	100	20	0.26	L1	
MT150DT08L2	800	150	93	1500	1.35	150	10	0.14	150	3.0	1.35	150	40	0.16	L2	
MT150DT12L2	1200	150	93	1500	1.35	150	10	0.14	150	3.0	1.35	150	40	0.16	L2	
MT150DT16L2	1600	150	93	1500	1.35	150	10	0.14	150	3.0	1.35	150	40	0.16	L2	
MT150DT18L2	1800	150	93	1500	1.35	150	10	0.14	150	3.0	1.35	150	40	0.16	L2	
MT200DT08L2	800	200	93	1900	1.35	200	10	0.12	200	3.0	1.40	200	100	0.14	L2	
MT200DT12L2	1200	200	93	1900	1.35	200	10	0.12	200	3.0	1.40	200	100	0.14	L2	
MT200DT16L2	1600	200	93	1900	1.35	200	10	0.12	200	3.0	1.40	200	100	0.14	L2	
MT200DT18L2	1800	200	93	1900	1.35	200	10	0.12	200	3.0	1.40	200	100	0.14	L2	

L1

L2

快恢复二极管模块
FRD DIODE MODULES

型 号 Part NO.	反向重复峰值电压 V_{RRM} (V)	正向平均电流 IF（AV）d=0.5 Tc=110℃ (A)	浪涌电流 IFSM t=10ms Tj=45℃ (A)	最大正向压降 VF@IF Tj=125℃		反向恢复时间 trr IF=1A,VR=30V, diF/dt=-200A/us(ns)	结-壳热阻 R_{thj-c} (℃/W)	绝缘耐压 Visol (V)	封 装 Package	电路结构 Circuit structure
				(V)	(A)					
MF100C06F1	600	100	1300	1.3	100	50	0.2	3000，1min	F1	
MF100C12F1	1200	100	1100	1.35	100	55	0.2	3000，1min	F1	
MF100A06F1	600	100	1300	1.3	100	50	0.2	3000，1min	F1	
MF100A12F1	1200	100	1100	1.35	100	55	0.2	3000，1min	F1	
MF100K06F1	600	100	1300	1.3	100	50	0.2	3000，1min	F1	
MF100K12F1	1200	100	1100	1.35	100	55	0.2	3000，1min	F1	
MF150C06F2	600	150	1400	1.45	150	50	0.17	3000，1min	F2	
MF200C06F2	600	200	2000	1.25	200	50	0.18	3000，1min	F2	
MF300C06F2	600	300	3000	1.45	300	55	1.14	3000，1min	F2	
MF200C12F2	1200	200	1800	1.9	200	57	0.11	3000，1min	F2	
MF300C12F2	1200	300	2700	2.4	300	65	0.07	3000，1min	F2	
MF100C12F2	1200	100	1100	1.35	100	55	0.11	3000，1min	F2	
MF150A06F2	600	150	1400	1.45	150	50	0.34	3000，1min	F2	
MF200A06F2	600	200	2000	1.25	200	50	0.18	3000，1min	F2	
MF200A12F2	1200	200	1800	1.9	200	57	0.11	3000，1min	F2	
MF300A06F2	600	300	3000	1.45	300	55	0.07	3000，1min	F2	
MF150K06F2	600	150	1400	1.45	150	50	0.34	3000，1min	F2	
MF200K06F2	600	200	2000	1.25	200	50	0.18	3000，1min	F2	
MF200K12F2	1200	200	1800	1.9	200	57	0.11	3000，1min	F2	
MF300K06F2	600	300	3000	1.45	300	55	1.14	3000，1min	F2	
MF300U06F2	600	300	3000	1.45	300	55	0.10	3000，1min	F2	
MF300U12F2	1200	300	2500	1.8	300	57	0.14	3000，1min	F2	
MF100U12F2	1200	100	1100	1.35	100	55	0.22	3000，1min	F2	
MF200U12F2	1200	200	1800	1.9	200	57	0.22	3000，1min	F2	
MF400U12F2	1200	400	3200	1.7	400	76	0.22	3000，1min	F2	
MF500U12F2	1200	500	5000	1.8	500	80	0.10	3000，1min	F2	
MF100A06F2N	600	100	1300	1.3	100	50	0.11	3000，1min	F2N	
MF150A06F2N	600	150	1400	1.45	150	50	0.11	3000，1min	F2N	
MF200A06F2N	600	200	2000	1.25	200	50	0.11	3000，1min	F2N	
MF200A12F2N	1200	200	1800	1.9	200	57	0.11	3000，1min	F2N	
MF300A06F2N	600	300	3000	1.45	300	55	0.14	3000，1min	F2N	
MF100K06F2N	600	100	1300	1.3	100	50	0.11	3000，1min	F2N	
MF150K06F2N	600	150	1400	1.45	150	50	0.11	3000，1min	F2N	
MF200K06F2N	600	200	2000	1.25	200	50	0.11	3000，1min	F2N	
MF200K12F2N	1200	200	1800	1.9	200	57	0.11	3000，1min	F2N	
MF300K06F2N	600	300	3000	1.45	300	55	0.14	3000，1min	F2N	
MF100C12F2N	1200	100	1100	1.35	100	55	0.11	3000，1min	F2N	
MF200C12F2N	1200	200	1800	1.9	200	57	0.11	3000，1min	F2N	

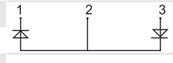
F1

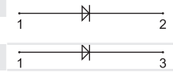
F2

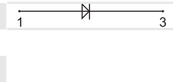
F2N

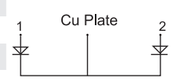
快恢复二极管模块
FRD DIODE MODULES

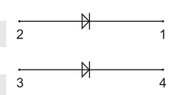
型 号 Part NO.	反向重复峰值电压 V_{RRM} (V)	正向平均电流 IF（AV）d=0.5 Tc=110℃ (A)	浪涌电流 IFSM t=10ms Tj=45℃ (A)	最大正向压降 VF@IF Tj=125℃ (V)	(A)	反向恢复时间 trr IF=1A,VR=30V, diF/dt=-200A/us(ns)	结-壳热阻 R_{thj-c} (℃/W)	绝缘耐压 Visol (V)	封 装 Package	电路结构 Circuit structure
MF100K06F5	600	100	1300	1.3	100	50	0.16	3000，1min	F5	
MF100K12F5	1200	100	1100	1.6	100	35	0.2	3000，1min	F5	
MF200K12F5	1200	200	1800	1.9	200	57	0.1	3000，1min	F5	
MF100A12F5	1200	100	1100	1.6	100	35	0.2	3000，1min	F5	
MF200A12F5	1200	200	1800	1.9	200	57	0.1	3000，1min	F5	
MF150C06F5	600	150	1400	1.4	150	50	0.16	3000，1min	F5	
MF200C12F5	1200	200	1800	1.9	200	57	0.1	3000，1min	F5	
MF300U05F6	500	300	5000	1.25	300	65	0.11	3000，1min	F6	
MF300U07F6	700	300	5000	1.45	300	72	0.12	3000，1min	F6	
MF400U12FD	1200	400	3200	1.7	400	76	0.11	3000，1min	FD	
MF200K04F3	400	2X100	1500	1.25	100	38	0.075	/	F3	
MF200K04F3LG	400	2X100	3000	1.15	100	50	0.07	/	F3	
MF200K06F3	600	2X100	2100	1.0	100	48	0.045	/	F3	
MF300K04F3	400	2X150	2700	0.90	150	44	0.05	/	F3	
MF300K04F3LG	400	2X150	4000	0.95	150	70	0.065	/	F3	
MF300K06F3	600	2X150	3500	1.25	150	50	0.03	/	F3	
MF400K04F3	400	2X200	4000	1.25	200	45	0.03	/	F3	
MF400K04F3LG	400	2X200	6000	0.95	200	80	0.06	/	F3	
MF400K06F3	600	2X200	3500	1.3	200	50	0.03	/	F3	
MF200K04F4	400	2X100	1500	1.25	100	38	0.15	/	F4	
MF200K06F4	600	2X100	2100	1.0	100	48	0.1	/	F4	
MF200K04F4N	400	2X100	1500	1.25	100	38	0.11	/	F4N	
MF200K06F4N	600	2X100	2100	1.0	100	48	0.1	/	F4N	
MF120DU06FJ	600	2X60	550	1.7	60	50	0.3	3000，1min	FJ	
MF120DU12FJ	1200	2X60	500	1.75	60	50	0.3	3000，1min	FJ	
MF200DU04FJ	400	2X100	1500	1.2	100	38	0.16	3000，1min	FJ	
MF200DU06FJ	600	2X100	1300	1.2	100	50	0.15	3000，1min	FJ	
MF200DU12FJ	1200	2X100	1450	1.38	100	45	0.16	3000，1min	FJ	











F5

F6

FD

F3

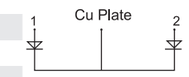
F4

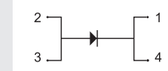
F4N

FJ

肖特基模块
SCHOTTKY MODULES

型 号 Part NO.	反向重复峰值电压 V_{RRM} (V)	正向平均电流 $I_{F(AV)}$ d=0.5 Tc=125℃ (A)	浪涌电流 I_{FSM} t=8.3ms Tj=45℃ (A)	正向压降 V_F @ I_F Tj=125℃ (V)	(A)	结-壳热阻 R_{thj-c} per chip (℃/W)	绝缘耐压 Visol (V)	封 装 Package	电路结构 Circuit structure
MB200K01F3	100	2X100	1500	0.68	100	0.15	/	F3	
MB400K01F3	100	2X200	3000	0.68	200	0.15	/	F3	
MB400K02F3	200	2x200	3000	0.78	200	0.15	/	F3	
MB600K01F3	100	2X300	4000	0.78	300	0.14	/	F3	
MB800K01F3	100	2X400	5800	0.82	400	0.15	/	F3	
MB400K01F4	100	2X200	3000	0.68	200	0.15	/	F4	
MB400K02F4	200	2X200	3000	0.78	200	0.15	/	F4	
MB400K01F4N	100	2X200	3000	0.68	200	0.15	/	F4N	
MB400K02F4N	200	2X200	3000	0.78	200	0.15	/	F4N	
MB200DU01FJ	100	2X100	1500	0.68	100	0.15	3000，1min	FJ	
MB200DU02FJ	200	2X100	1500	0.79	100	0.16	3000，1min	FJ	
MB300U02FJ	200	300	4750	0.90	300	0.13	3000，1min	FJ	





F3

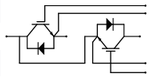
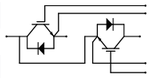
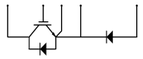
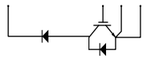
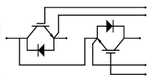
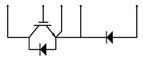
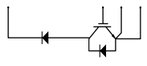
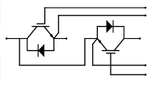
F4

F4N

FJ

IGBT模块
IGBT MODULES

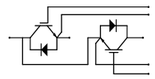
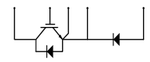
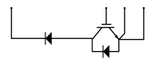
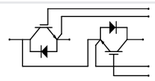
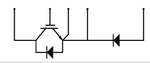
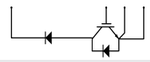
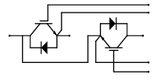
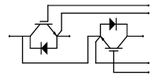
绝缘耐压：3000V(交流)
VISO:3000V(AC)

型 号 Part Number	集电极-发射极电压 V_{CES} min. (V)	集电极电流 Ic @ Tc=80℃ (A)	饱和压降 $V_{CE(sat)}$ typ. (V)	开关能量损耗典型值 Eon+Eoff typ. Tj=125℃ (mJ)	最大结-壳热阻 R_{thj-c} max. (C/W)	封 装 Package	电路结构 Circuit structure
MG75HF12MIC1	1200	75	1.9	9.3	0.19	C1	
MG100HF12MIC1	1200	100	1.85	12.86	0.17	C1	
MG150HF12MIC1	1200	150	1.8	15.3	0.15	C1	
MG75HF12MRC1	1200	75	2.3	15.1	0.2	C1	
MG100HF12MRC1	1200	100	2.3	17.7	0.18	C1	
MG150HF12MRC1	1200	150	2.3	19.8	0.16	C1	
MG50HF06LVC1	600	50	1.6	2.38	0.24	C1	
MG75HF06LVC1	600	75	1.6	3.71	0.2	C1	
MG100HF06LVC1	600	100	1.6	5.7	0.16	C1	
MG150HF06LVC1	600	150	1.6	8.55	0.13	C1	
MG200HF06LVC1	600	200	1.6	10.34	0.09	C1	
MG50ZU06LVC1	600	50	1.6	2.38	0.24	C1	
MG75ZU06LVC1	600	75	1.6	3.71	0.2	C1	
MG100ZU06LVC1	600	100	1.6	5.7	0.16	C1	
MG150ZU06LVC1	600	150	1.6	8.55	0.13	C1	
MG200ZU06LVC1	600	200	1.6	10.34	0.09	C1	
MG50ZD06LVC1	600	50	1.6	2.38	0.24	C1	
MG75ZD06LVC1	600	75	1.6	3.71	0.2	C1	
MG100ZD06LVC1	600	100	1.6	5.7	0.16	C1	
MG150ZD06LVC1	600	150	1.6	8.55	0.13	C1	
MG200ZD06LVC1	600	200	1.6	10.34	0.09	C1	
MG50HF065TYC1	650	50	1.6	2.58	0.24	C1	
MG75HF065TYC1	650	75	1.6	4.21	0.2	C1	
MG100HF065TYC1	650	100	1.6	6.2	0.16	C1	
MG150HF065TYC1	650	150	1.6	9.35	0.13	C1	
MG200HF065TYC1	650	200	1.6	11.54	0.09	C1	
MG50ZU065TYC1	650	50	1.6	2.58	0.24	C1	
MG75ZU065TYC1	650	75	1.6	4.21	0.2	C1	
MG100ZU065TYC1	650	100	1.6	6.2	0.16	C1	
MG150ZU065TYC1	650	150	1.6	9.35	0.13	C1	
MG200ZU065TYC1	650	200	1.6	11.54	0.09	C1	
MG50ZD065TYC1	650	50	1.6	2.58	0.24	C1	
MG75ZD065TYC1	650	75	1.6	4.21	0.2	C1	
MG100ZD065TYC1	650	100	1.6	6.2	0.16	C1	
MG150ZD065TYC1	650	150	1.6	9.35	0.13	C1	
MG200ZD065TYC1	650	200	1.6	11.54	0.09	C1	
MG40HF12LVC1	1200	40	1.85	10.07	0.3	C1	
MG50HF12LVC1	1200	50	1.85	11.88	0.27	C1	
MG75HF12LVC1	1200	75	1.85	15.96	0.22	C1	
MG100HF12LVC1	1200	100	1.85	17.48	0.18	C1	
MG150HF12LVC1	1200	150	1.85	19.85	0.13	C1	

C1

IGBT模块
IGBT MODULES

绝缘耐压：3000V(交流)
VISO:3000V(AC)

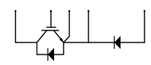
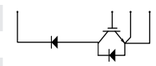
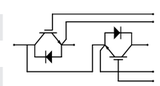
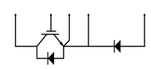
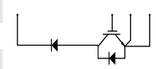
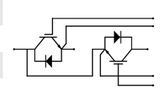
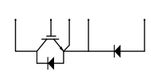
型 号 Part Number	集电极-发射极电压 V_{CES} min. (V)	集电极电流 Ic @ Tc=80℃ (A)	饱和压降 $V_{CE(sat)}$ typ. (V)	开关能量损耗典型值 Eon+Eoff typ. Tj=125℃ (mJ)	最大结-壳热阻 R_{thj-c} max. (C/W)	封 装 Package	电路结构 Circuit structure
MG40HF12LEC1	1200	40	3	6.94	0.37	C1	
MG50HF12LEC1	1200	50	3	8.17	0.33	C1	
MG75HF12LEC1	1200	75	3	8.74	0.29	C1	
MG100HF12LEC1	1200	100	3	12.07	0.2	C1	
MG50ZU12LVC1	1200	50	1.85	11.86	0.27	C1	
MG75ZU12LVC1	1200	75	1.85	15.96	0.22	C1	
MG100ZU12LVC1	1200	100	1.85	17.48	0.18	C1	
MG50ZU12LEC1	1200	50	3	8.17	0.33	C1	
MG75ZU12LEC1	1200	75	3	8.74	0.29	C1	
MG100ZU12LEC1	1200	100	3	12.07	0.2	C1	
MG50ZD12LVC1	1200	50	1.85	11.86	0.27	C1	
MG75ZD12LVC1	1200	75	1.85	15.96	0.22	C1	
MG100ZD12LVC1	1200	100	1.85	17.48	0.18	C1	
MG50ZD12LEC1	1200	50	3	8.17	0.33	C1	
MG75ZD12LEC1	1200	75	3	8.74	0.29	C1	
MG100ZD12LEC1	1200	100	3	12.07	0.2	C1	
MG50HF17LVC1	1700	50	2.3	38.48	0.22	C1	
MG75HF17LVC1	1700	75	2.3	56.05	0.17	C1	
MG100HF17LVC1	1700	100	2.3	76	0.14	C1	
MG50ZU17LVC1	1700	50	2.3	38.48	0.22	C1	
MG75ZU17LVC1	1700	75	2.3	56.05	0.17	C1	
MG100ZU17LVC1	1700	100	2.3	76	0.14	C1	
MG50ZD17LVC1	1700	50	2.3	38.48	0.22	C1	
MG75ZD17LVC1	1700	75	2.3	56.05	0.17	C1	
MG100ZD17LVC1	1700	100	2.3	76	0.14	C1	
MG150HF12MRC2	1200	150	2.3	33.6	0.11	C2	
MG200HF12MRC2	1200	200	2.3	46.4	0.09	C2	
MG300HF12MRC2	1200	300	2.3	61.2	0.075	C2	
MG400HF12MRC2	1200	400	2.4	77.9	0.065	C2	
MG150HF12MIC2	1200	150	1.9	24.5	0.1	C2	
MG200HF12MIC2	1200	200	1.85	31.3	0.08	C2	
MG300HF12MIC2	1200	300	1.8	53	0.07	C2	
MG400HF12MIC2	1200	400	1.8	57.7	0.06	C2	
MG200HF06LVC2	600	200	1.45	11.02	0.21	C2	
MG300HF06LVC2	600	300	1.45	15.01	0.15	C2	
MG400HF06LVC2	600	400	1.45	17.96	0.11	C2	
MG600HF06LVC2	600	600	1.45	33.25	0.09	C2	
MG200HF06LEC2	600	200	2.8	13.49	0.11	C2	
MG300HF06LEC2	600	300	2.8	21.38	0.1	C2	
MG400HF06LEC2	600	400	2.8	28.5	0.08	C2	

C1

C2

IGBT模块
IGBT MODULES

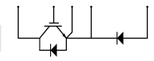
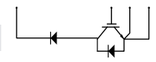
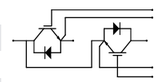
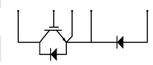
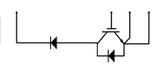
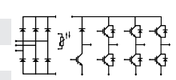
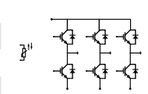
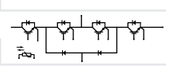
绝缘耐压：3000V(交流)
Viso:3000V(AC)

型 号 Part Number	集电极-发射极电压 V_{CES} min. (V)	集电极电流 Ic @ Tc=80°C (A)	饱和压降 $V_{CE(sat)}$ typ. (V)	开关能量损耗典型值 Eon+Eoff typ. Tj=125°C (mJ)	最大结-壳热阻 R_{thj-c} max. (C/W)	封 装 Package	电路结构 Circuit structure
MG200ZU06LVC2	600	200	1.45	11.02	0.21	C2	
MG300ZU06LVC2	600	300	1.45	15.01	0.15	C2	
MG400ZU06LVC2	600	400	1.45	17.96	0.11	C2	
MG600ZU06LVC2	600	600	1.45	33.25	0.09	C2	
MG200ZU06LEC2	600	200	2.8	13.49	0.11	C2	
MG300ZU06LEC2	600	300	2.8	21.38	0.1	C2	
MG400ZU06LEC2	600	400	2.8	28.5	0.08	C2	
MG200ZD06LVC2	600	200	1.45	11.02	0.21	C2	
MG300ZD06LVC2	600	300	1.45	15.01	0.15	C2	
MG400ZD06LVC2	600	400	1.45	17.96	0.11	C2	
MG600ZD06LVC2	600	600	1.45	33.25	0.09	C2	
MG200ZD06LEC2	600	200	2.8	13.49	0.11	C2	
MG300ZD06LEC2	600	300	2.8	21.38	0.1	C2	
MG400ZD06LEC2	600	400	2.8	28.5	0.08	C2	
MG200HF065TYC2	650	200	1.45	12.02	0.21	C2	
MG300HF065TYC2	650	300	1.45	16.01	0.15	C2	
MG400HF065TYC2	650	400	1.45	19.23	0.11	C2	
MG600HF065TYC2	650	600	1.45	36.35	0.09	C2	
MG200ZU065TYC2	650	200	1.45	12.02	0.21	C2	
MG300ZU065TYC2	650	300	1.45	16.01	0.15	C2	
MG400ZU065TYC2	650	400	1.45	19.23	0.11	C2	
MG600ZU065TYC2	650	600	1.45	36.35	0.09	C2	
MG200ZD065TYC2	650	200	1.45	12.02	0.21	C2	
MG300ZD065TYC2	650	300	1.45	16.01	0.15	C2	
MG400ZD065TYC2	650	400	1.45	19.23	0.11	C2	
MG600ZD065TYC2	650	600	1.45	36.35	0.09	C2	
MG100HF12LVC2	1200	100	1.9	17.48	0.14	C2	
MG150HF12LVC2	1200	150	1.9	34.2	0.11	C2	
MG200HF12LVC2	1200	200	1.9	37.05	0.1	C2	
MG300HF12LVC2	1200	300	1.9	60.8	0.08	C2	
MG400HF12LVC2	1200	400	1.9	80.75	0.05	C2	
MG450HF12LVC2	1200	450	1.9	90.1	0.04	C2	
MG100HF12LEC2	1200	100	3.1	12.07	0.15	C2	
MG150HF12LEC2	1200	150	3.1	18.05	0.11	C2	
MG200HF12LEC2	1200	200	3.1	28.5	0.09	C2	
MG300HF12LEC2	1200	300	3.1	48.45	0.06	C2	
MG400HF12LEC2	1200	400	3.1	57	0.05	C2	
MG100ZU12LVC2	1200	100	1.9	17.48	0.14	C2	
MG150ZU12LVC2	1200	150	1.9	34.2	0.11	C2	
MG200ZU12LVC2	1200	200	1.9	37.05	0.1	C2	
MG300ZU12LVC2	1200	300	1.9	60.8	0.08	C2	
MG400ZU12LVC2	1200	400	1.9	80.75	0.05	C2	

C2

IGBT模块
IGBT MODULES

绝缘耐压：3000V(交流)
Viso:3000V(AC)

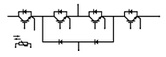
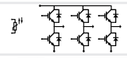
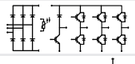
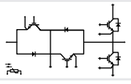
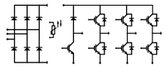
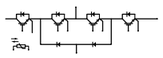
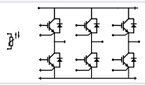
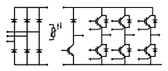
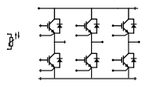
型 号 Part Number	集电极-发射极电压 V_{CES} min. (V)	集电极电流 Ic @ Tc=80°C (A)	饱和压降 $V_{CE(sat)}$ typ. (V)	开关能量损耗典型值 Eon+Eoff typ. Tj=125°C (mJ)	最大结-壳热阻 R_{thj-c} max. (C/W)	封 装 Package	电路结构 Circuit structure
MG450ZU12LVC2	1200	450	1.9	90.1	0.04	C2	
MG100ZU12LEC2	1200	100	3.1	12.07	0.15	C2	
MG150ZU12LEC2	1200	150	3.1	18.05	0.11	C2	
MG200ZU12LEC2	1200	200	3.1	28.5	0.09	C2	
MG300ZU12LEC2	1200	300	3.1	48.45	0.06	C2	
MG400ZU12LEC2	1200	400	3.1	57	0.05	C2	
MG100ZD12LVC2	1200	100	1.9	17.48	0.14	C2	
MG150ZD12LVC2	1200	150	1.9	34.2	0.11	C2	
MG200ZD12LVC2	1200	200	1.9	37.05	0.1	C2	
MG300ZD12LVC2	1200	300	1.9	60.8	0.08	C2	
MG400ZD12LVC2	1200	400	1.9	80.75	0.05	C2	
MG450ZD12LVC2	1200	450	1.9	90.1	0.04	C2	
MG100ZD12LEC2	1200	100	3.1	12.07	0.15	C2	
MG150ZD12LEC2	1200	150	3.1	18.05	0.11	C2	
MG200ZD12LEC2	1200	200	3.1	28.5	0.09	C2	
MG300ZD12LEC2	1200	300	3.1	48.45	0.06	C2	
MG400ZD12LEC2	1200	400	3.1	57	0.05	C2	
MG100HF17LVC2	1700	100	2.3	90.23	0.16	C2	
MG150HF17LVC2	1700	150	2.3	115.34	0.12	C2	
MG200HF17LVC2	1700	200	2.3	147.25	0.08	C2	
MG300HF17LVC2	1700	300	2.3	209	0.05	C2	
MG400HF17LVC2	1700	400	2.3	275.5	0.04	C2	
MG100ZU17LVC2	1700	100	2.3	90.23	0.16	C2	
MG150ZU17LVC2	1700	150	2.3	115.34	0.12	C2	
MG200ZU17LVC2	1700	200	2.3	147.25	0.08	C2	
MG300ZU17LVC2	1700	300	2.3	209	0.05	C2	
MG400ZU17LVC2	1700	400	2.3	275.5	0.04	C2	
MG100ZD17LVC2	1700	100	2.3	90.23	0.16	C2	
MG150ZD17LVC2	1700	150	2.3	115.34	0.12	C2	
MG200ZD17LVC2	1700	200	2.3	147.25	0.08	C2	
MG300ZD17LVC2	1700	300	2.3	209	0.05	C2	
MG400ZD17LVC2	1700	400	2.3	275.5	0.04	C2	
MG10P06P2	600	10	1.65	0.89	0.92	P2	
MG20P06P2	600	20	1.65	1.24	0.62	P2	
MG10P120P2	1200	10	1.85	1.53	1.43	P2	
MG15P120P2	1200	15	1.85	2.58	1.05	P2	
MG20TF06P2	600	20	1.65	1.24	0.62	P2	
MG30TF06P2	600	30	1.65	1.81	0.44	P2	
MG25TF12P2	1200	25	1.85	4.55	0.38	P2	
MG35TF12P2	1200	35	1.85	6.25	0.27	P2	
MG30TL06P2	600	30	1.65	1.81	0.44	P2	
MG50TL06P2	600	50	1.65	2.57	0.37	P2	

C2

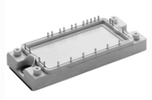
P2

IGBT模块
IGBT MODULES

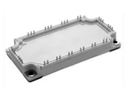
绝缘耐压：3000V(交流)
VISO:3000V(AC)

型 号 Part Number	集电极-发射极电压 V_{CES} min. (V)	集电极电流 I_C @ T_C=80°C (A)	饱和压降 $V_{CE(sat)}$ typ. (V)	开关能量损耗典型值 Eon+Eoff typ. Tj=125°C (mJ)	最大结-壳热阻 R_{thj-c} max. (C/W)	封 装 Package	电路结构 Circuit structure
MG75TL065P3	650	75	1.65	5.61	0.33	P3	
MG100TL065P3	650	100	1.65	8.55	0.24	P3	
MG150TL065P3	650	150	1.65	13.4	0.17	P3	
MG50TF12P3	1200	50	1.85	9.41	0.18	P3	
MG75TF12P3	1200	75	1.85	12.35	0.11	P3	
MG25P12P3	1200	25	1.85	4.56	0.68	P3	
MG35P12P3	1200	35	1.85	6.27	0.43	P3	
MG100TT12LEP3	1200	100	1.55	10.21	0.18	P3	
MG150TT12LEP3	1200	150	1.55	14.22	0.16	P3	
MG200TT12LEP3	1200	200	1.55	18.21	0.12	P3	
MG10P06E1	600	10	1.6	0.48	1.43	E1	
MG15P06E1	600	15	1.6	0.62	1.24	E1	
MG25P06E1	600	25	1.6	0.95	0.95	E1	
MG35P06E1	600	35	1.6	1.43	0.67	E1	
MG40P06E1	600	40	1.6	2.85	0.59	E1	
MG10P065E1	650	10	1.6	0.52	1.43	E1	
MG15P065E1	650	15	1.6	0.68	1.24	E1	
MG25P065E1	650	25	1.6	1.12	0.95	E1	
MG35P065E1	650	35	1.6	1.63	0.67	E1	
MG40P065E1	650	40	1.6	3.15	0.59	E1	
MG10P12E1	1200	10	1.85	1.52	1.14	E1	
MG15P12E1	1200	15	1.85	2.57	0.87	E1	
MG25P12E1	1200	25	1.85	4.56	0.66	E1	
MG40P12E1	1200	40	1.85	7.41	0.4	E1	
MG35TF12E1	1200	35	1.85	6.27	0.42	E1	
MG50TF12E1	1200	50	1.85	10.45	0.39	E1	
MG75TF12E1	1200	75	1.85	14.62	0.33	E1	
MG10P065E1A	650	10	1.6	0.52	1.43	E1A	
MG15P065E1A	650	15	1.6	0.68	1.24	E1A	
MG25P065E1A	650	25	1.6	1.12	0.95	E1A	
MG35P065E1A	650	35	1.6	1.63	0.67	E1A	
MG50P065E1A	650	50	1.6	3.15	0.59	E1A	
MG15P12E1A	1200	15	1.85	2.57	0.87	E1A	
MG25P12E1A	1200	25	1.85	4.56	0.66	E1A	
MG35P12E1A	1200	35	1.85	6.27	0.42	E1A	
MG50P12E1A	1200	50	1.85	10.45	0.39	E1A	
MG50TF065E2A	650	50	1.65	2.85	0.59	E2A	
MG75TF065E2A	650	75	1.65	4.28	0.47	E2A	
MG100TF065E2A	650	100	1.65	6.65	0.36	E2A	
MG150TF065E2A	650	150	1.65	10.93	0.27	E2A	


P3

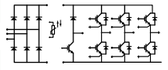
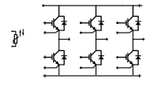
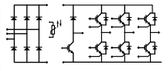
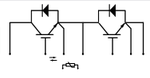
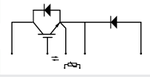
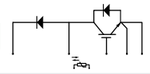
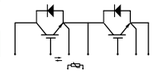
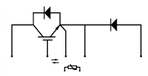
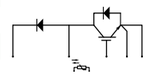
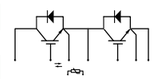

E1


E1A

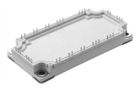

E2A

IGBT模块
IGBT MODULES

绝缘耐压：3000V(交流)
VISO:3000V(AC)

型 号 Part Number	集电极-发射极电压 V_{CES} min. (V)	集电极电流 I_C @ T_C=80°C (A)	饱和压降 $V_{CE(sat)}$ typ. (V)	开关能量损耗典型值 Eon+Eoff typ. Tj=125°C (mJ)	最大结-壳热阻 R_{thj-c} max. (C/W)	封 装 Package	电路结构 Circuit structure
MG50P065E2A	650	50	1.65	2.85	0.59	E2A	
MG75P065E2A	650	75	1.65	4.28	0.47	E2A	
MG100P065E2A	650	100	1.65	6.65	0.36	E2A	
MG50P12E2A	1200	50	1.85	11.88	0.41	E2A	
MG75P12E2A	1200	75	1.85	15.96	0.33	E2A	
MG50TF12E2A	1200	50	1.85	11.88	0.41	E2A	
MG75TF12E2A	1200	75	1.85	15.96	0.33	E2A	
MG100TF12E2A	1200	100	1.85	17.48	0.2	E2A	
MG150TF12E2A	1200	150	1.85	34.2	0.17	E2A	
MG200TF12E2A	1200	200	1.85	45.2	0.13	E2A	
MG50P12E2	1200	50	1.85	11.88	0.41	E2	
MG75P12E2	1200	75	1.85	15.96	0.33	E2	
MG100P12E2	1200	100	1.85	17.48	0.2	E2	
MG150P12E2	1200	150	1.85	34.2	0.17	E2	
MG300HF065E3	650	300	1.45	30	0.2	E3	
MG450HF065E3	650	450	1.45	43	0.09	E3	
MG600HF065E3	650	600	1.45	54	0.06	E3	
MG300ZU065E3	650	300	1.45	30	0.2	E3	
MG450ZU065E3	650	450	1.45	43	0.09	E3	
MG600ZU065E3	650	600	1.45	54	0.06	E3	
MG300ZD065E3	650	300	1.45	30	0.2	E3	
MG450ZD065E3	650	450	1.45	43	0.09	E3	
MG600ZD065E3	650	600	1.45	54	0.06	E3	
MG150HF12E3	1200	150	1.85	34	0.08	E3	
MG225HF12E3	1200	225	1.85	43	0.07	E3	
MG300HF12E3	1200	300	1.85	62	0.04	E3	
MG450HF12E3	1200	450	1.85	91	0.03	E3	
MG600HF12E3	1200	600	1.85	121	0.02	E3	
MG150ZU12E3	1200	150	1.85	34	0.08	E3	
MG225ZU12E3	1200	225	1.85	43	0.07	E3	
MG300ZU12E3	1200	300	1.85	62	0.04	E3	
MG450ZU12E3	1200	450	1.85	91	0.03	E3	
MG600ZU12E3	1200	600	1.85	121	0.02	E3	
MG150ZD12E3	1200	150	1.85	34	0.08	E3	
MG225ZD12E3	1200	225	1.85	43	0.07	E3	
MG300ZD12E3	1200	300	1.85	62	0.04	E3	
MG450ZD12E3	1200	450	1.85	91	0.03	E3	
MG600ZD12E3	1200	600	1.85	121	0.02	E3	
MG150HF17E3	1700	150	2.4	105	0.08	E3	
MG225HF17E3	1700	225	2.4	153	0.07	E3	
MG300HF17E3	1700	300	2.4	210	0.04	E3	
MG450HF17E3	1700	450	2.4	295	0.04	E3	
MG600HF17E3	1700	600	2.4	352	0.03	E3	

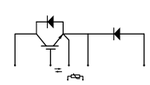
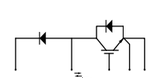
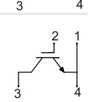

E2A


E2


E3

IGBT模块
IGBT MODULES

绝缘耐压：3000V(交流)
Viso:3000V(AC)

型 号 Part Number	集电极-发射极电压 V_{CES} min. (V)	集电极电流 Ic @ Tc=80℃ (A)	饱和压降 $V_{CE(sat)}$ typ. (V)	开关能量损耗典型值 Eon+Eoff typ. Tj=125℃ (mJ)	最大结-壳热阻 R_{thj-c} max. (℃/W)	封 装 Package	电路结构 Circuit structure
MG150ZU17E3	1700	150	2.4	105	0.08	E3	
MG225ZU17E3	1700	225	2.4	153	0.07	E3	
MG300ZU17E3	1700	300	2.4	210	0.04	E3	
MG450ZU17E3	1700	450	2.4	295	0.04	E3	
MG600ZU17E3	1700	600	2.4	352	0.03	E3	
MG150ZD17E3	1700	150	2.4	105	0.08	E3	
MG225ZD17E3	1700	225	2.4	153	0.07	E3	
MG300ZD17E3	1700	300	2.4	210	0.04	E3	
MG450ZD17E3	1700	450	2.4	295	0.04	E3	
MG600ZD17E3	1700	600	2.4	352	0.03	E3	
MG75U12MRGJ	1200	75	2.3	18.1	0.2	GJ	
MG75UZ12MRGJ	1200	75	2.3	18.1	0.2	GJ	
MG100UZ12MRGJ	1200	100	2.3	17.7	0.18	GJ	


E3


GJ

IGBT单管
IGBT DISCRETE

型 号 Part Number	集电极-发射极电压 V_{CES} min. (V)	集电极电流 Ic @ Tc=80℃ (A)	饱和压降 $V_{CE(sat)}$ typ. (V)	开关能量损耗典型值 Eon+Eoff typ. Tj=125℃ (mJ)	最大结-壳热阻 R_{thj-c} max. (℃/W)	封 装 Package	电路结构 Circuit structure
DGF15N65T1	650	15	1.65	0.85	4.9	TO-220F	
DGF20N65T1	650	20	1.9	1.2	4.9	TO-220F	
DGK15N65T1	650	15	1.65	0.85	1.2	TO-263	
DGK20N65T1	650	20	1.9	1.2	1.2	TO-263	
DGP15N65T1	650	15	1.65	0.85	1.2	TO-220	
DGP20N65T1	650	20	1.9	1.2	1.2	TO-220	
DGW10N120T1	1200	10	1.6	1.37	0.69	TO-247	
DGW15N120T1	1200	15	1.7	2.21	0.65	TO-247	
DGW25N120T1	1200	25	1.65	2.95	0.5	TO-247	
DGW25N135F1A	1350	25	2	2.68	0.48	TO-247	
DGW30N65F1	650	30	1.9	1.8	0.8	TO-247	
DGW30N65F1A	650	30	1.66	2.65	0.52	TO-247	
DGW30N120F1	1200	30	1.75	2.65	0.5	TO-247	
DGW40N120T1B1	1200	40	1.7	3.9	0.3	TO-247	
DGW60N65F1A1	650	60	1.85	3.09	0.48	TO-247	
DGW60N65T1	650	60	1.85	3.09	0.48	TO-247	
DGW75N65T1	650	75	1.7	12.7	0.3	TO-247	
AUYJ40N120T1	1200	40	1.7	3.9	0.3	TO-247	

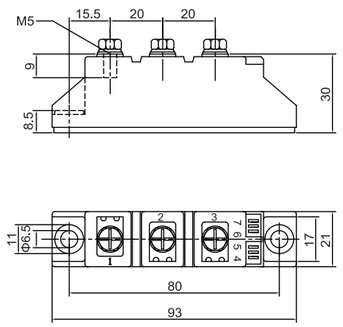

TO-220F

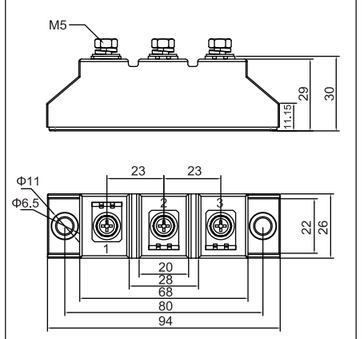

TO-263

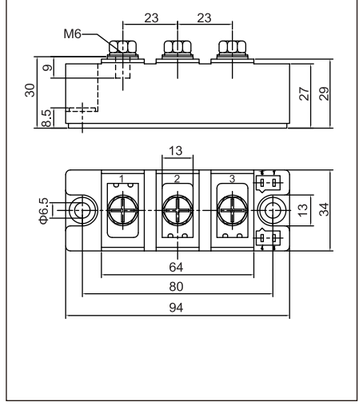

TO-220

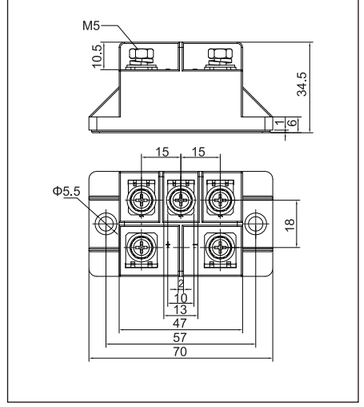

TO-247

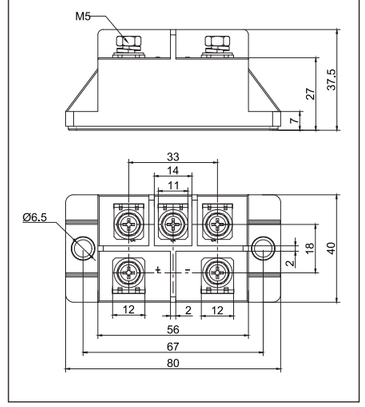
封装尺寸图
OUTLINE DRAWING

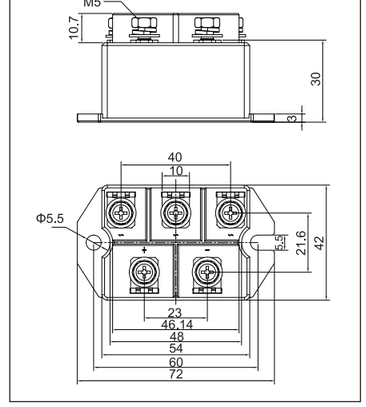
D1


D1N


D2


M7


M8


NM2


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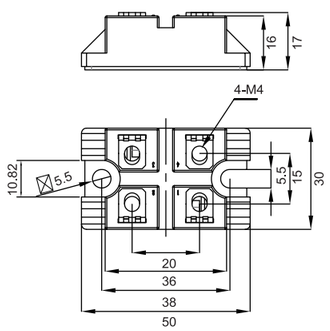

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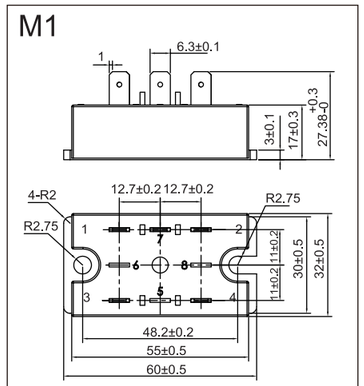

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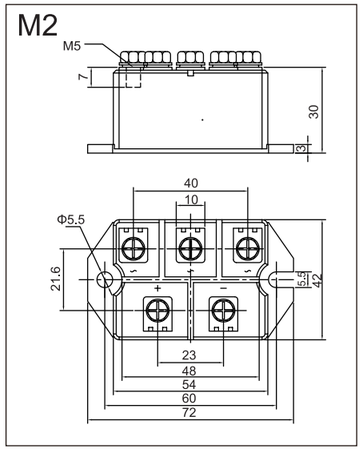

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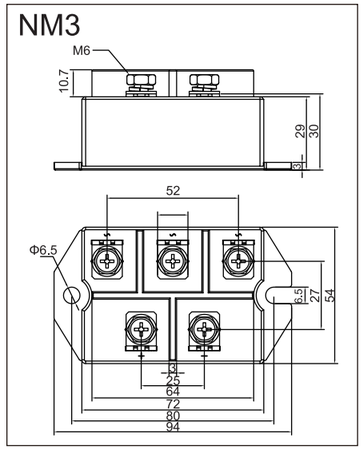

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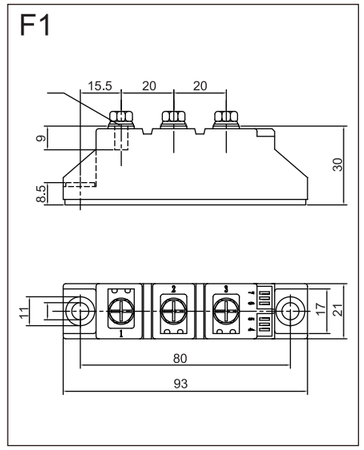

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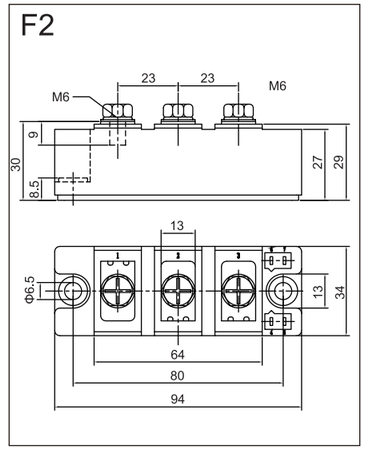

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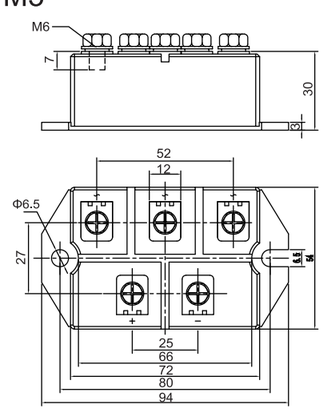

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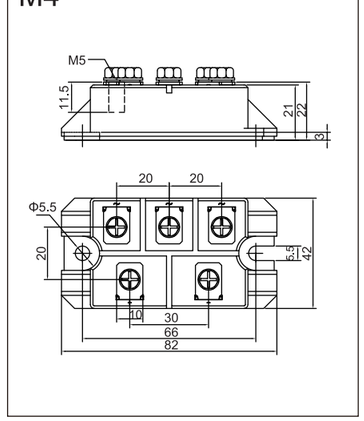

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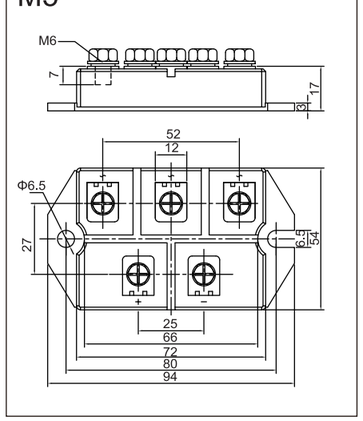

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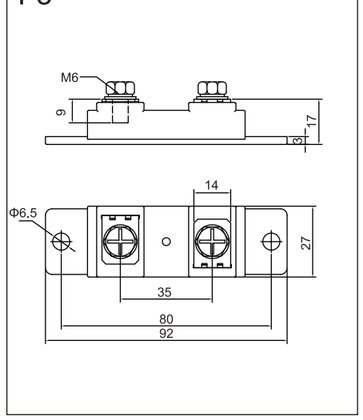

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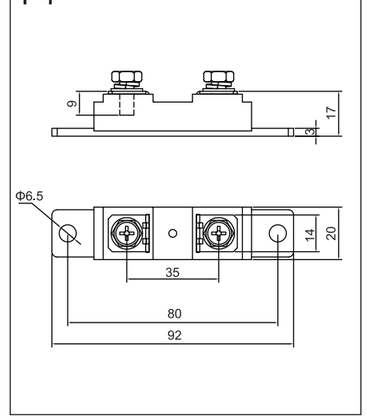

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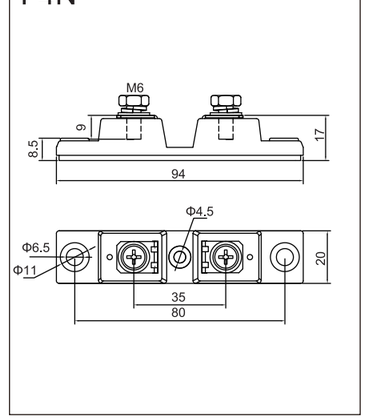

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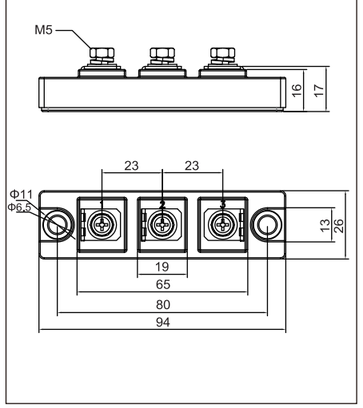

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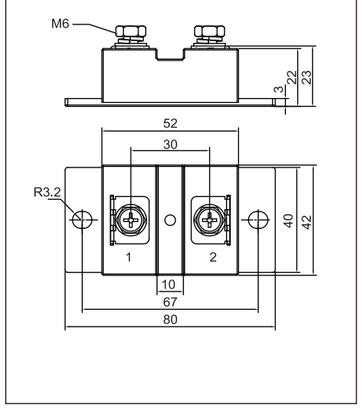
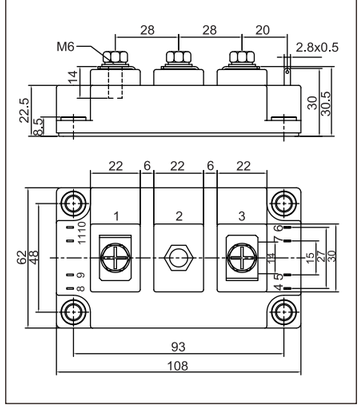


FD



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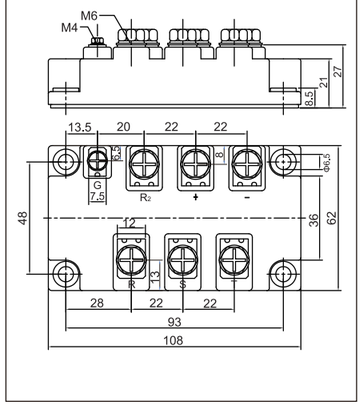

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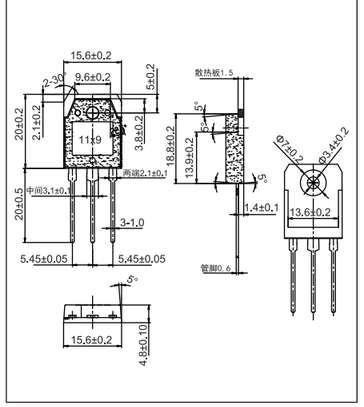

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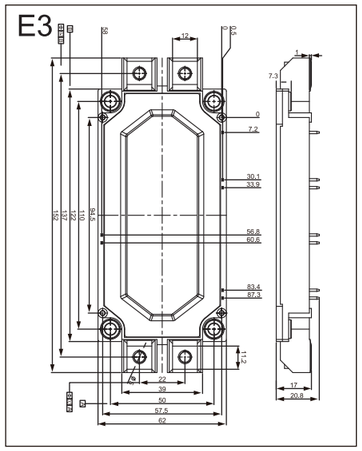

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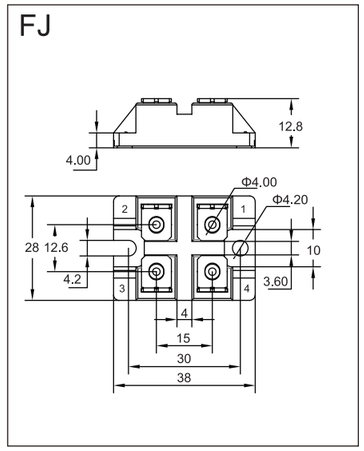

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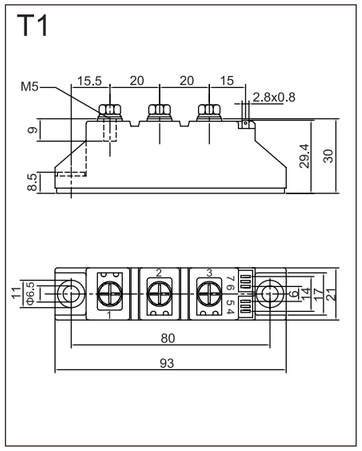

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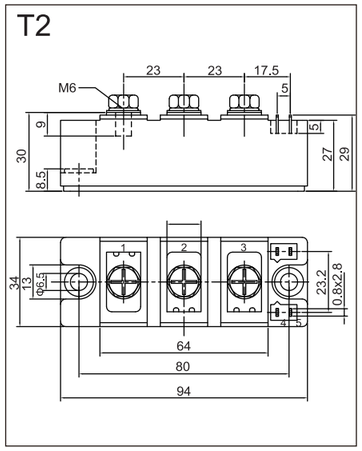

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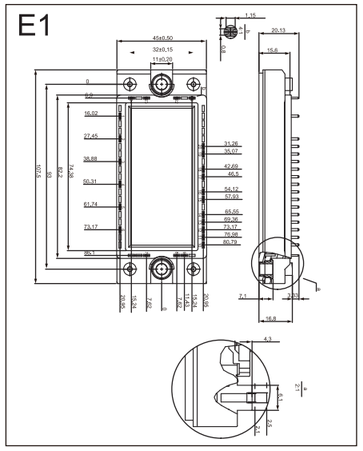

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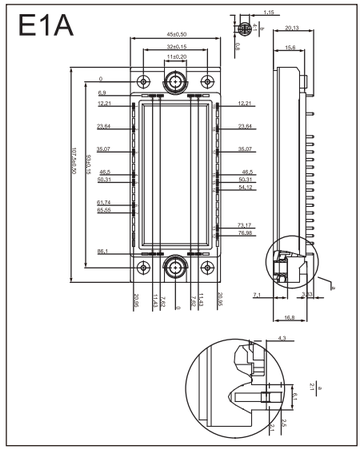

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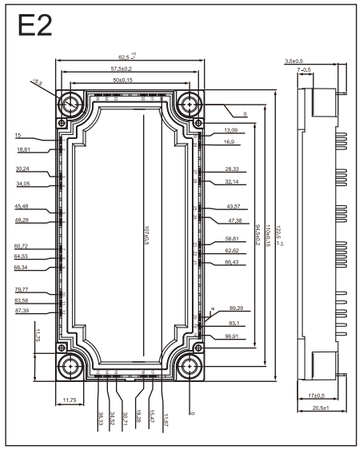

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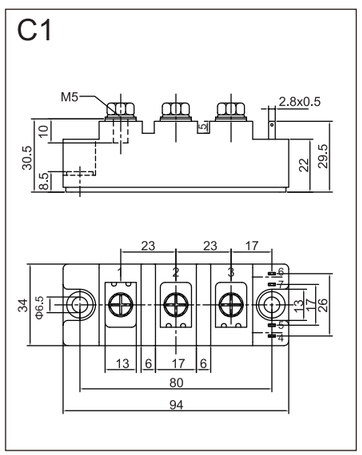

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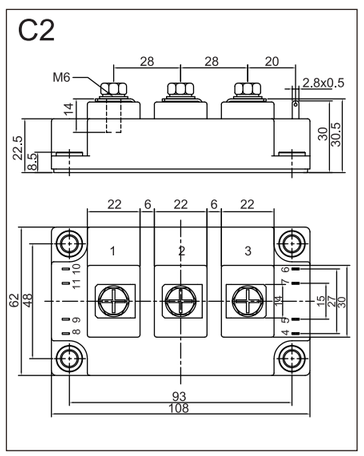

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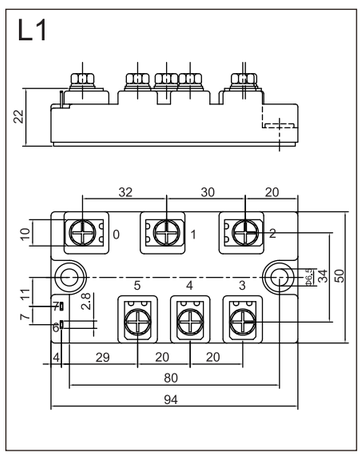

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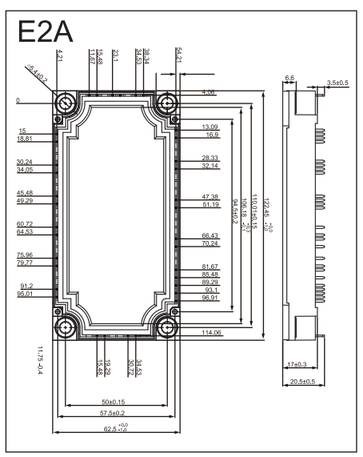

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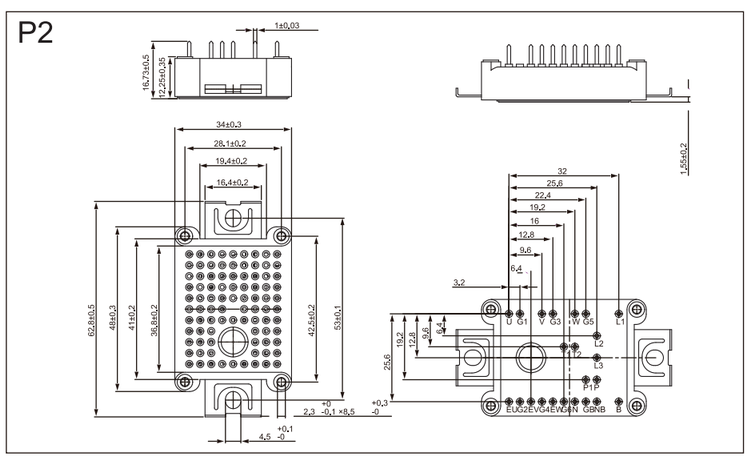

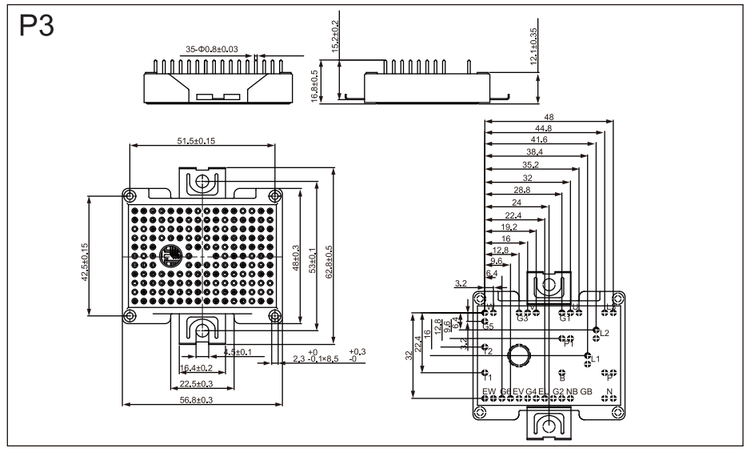

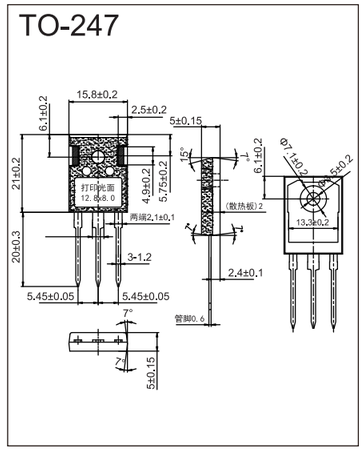

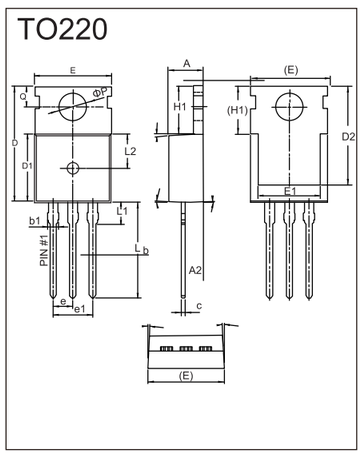

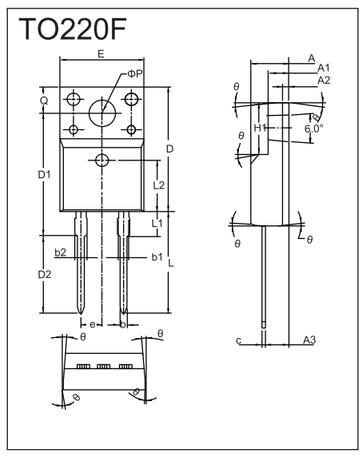

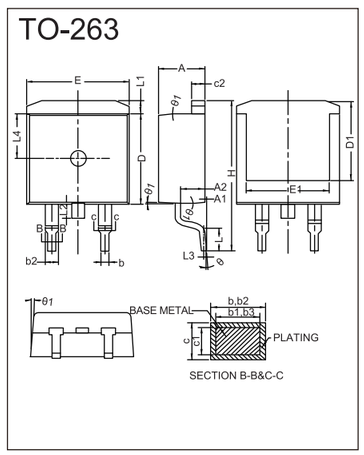

包装形态
PACKING

封装型号 Package No	包装代码 Packing Code	包装方式 Packing Method	只/盒 Pcs/Box	只/箱 Pcs/Carton	内盒尺寸(mm) Inner Box Size			外箱尺寸(mm) Carton Size			单盒重量(±0.3Kg) Single box weight		整箱重量(±0.5Kg) FCL weight	
					长(L)	宽(W)	高(H)	长(L)	宽(W)	高(H)	毛重(KG)	净重(KG)	毛重(KG)	净重(KG)
D1	A1	盒装	10	100	268	250	48	535	285	240	1.21	0.81	13.8	12.2
D1N	A1	盒装	8	80	268	250	48	535	285	240	1.072	0.672	11.5	9.9
D2	A1	盒装	8	80	268	250	48	535	285	240	1.626	1.226	17.1	15.5
DA	A1	盒装	12	120	268	250	48	535	285	240	0.787	0.387	8.7	7.1
M1	A1	盒装	15	90	268	250	48	535	285	240	1.34	0.94	8.6	7
M2	A1	盒装	8	80	268	250	48	535	285	240	1.337	0.937	14.1	12.5
M3	A1	盒装	6	60	268	250	48	535	285	240	1.655	1.255	17.3	15.7
M4	A1	盒装	6	60	268	250	48	535	285	240	1.118	0.718	12.3	10.7
M5	A1	盒装	6	60	268	250	48	535	285	240	1.487	1.087	15.7	14.1
M7	A1	盒装	6	60	268	250	48	535	285	240	0.935	0.535	10.1	8.5
M8	A1	盒装	6	60	268	250	48	535	285	240	1.167	0.767	12.5	10.9
NM2	A1	盒装	8	80	268	250	48	535	285	240	1.345	0.945	14.1	12.5
NM3	A1	盒装	6	60	268	250	48	535	285	240	1.66	1.26	17.3	15.7
F1	A1	盒装	10	100	268	250	48	535	285	240	1.194	0.794	12.8	11.2
F2	A1	盒装	8	80	268	250	48	535	285	240	1.602	1.202	16.8	15.2
F2N	A1	盒装	8	80	268	250	48	535	285	240	1.602	1.202	16.8	15.2
F3	A1	盒装	10	100	268	250	48	535	285	240	1.135	0.735	12.4	10.8
F4	A1	盒装	12	120	268	250	48	535	285	240	1.044	0.644	11.4	9.8
F4N	A1	盒装	12	120	268	250	48	535	285	240	1.044	0.644	11.4	9.8
F5	A1	盒装	10	100	268	250	48	535	285	240	1.14	0.74	13.1	11.5
F6	A1	盒装	6	60	268	250	48	535	285	240	1.616	1.216	16.4	14.8
FD	A1	盒装	4	40	268	250	48	535	285	240	1.58	1.18	16.8	15.2
FJ	A2	珍珠棉包装	25	125	280	126	52	555	310	280	0.96	0.56	5.4	3.8
GJ	A2	珍珠棉包装	25	125	280	126	52	555	310	280	1.154	0.754	11.5	9.9
T1	A1	盒装	10	100	268	250	48	535	285	240	1.21	0.81	13.8	12.2
T1D	A1	盒装	10	100	268	250	48	535	285	240	1.21	0.81	13.8	12.2
T2	A1	盒装	8	80	268	250	48	535	285	240	1.602	1.202	16.8	15.2
C1	A1	盒装	8	80	268	250	48	535	285	240	1.626	1.226	17.1	15.5
C2	A1	盒装	4	40	268	250	48	535	285	240	1.58	1.18	16.8	15.2
L1	A1	盒装	6	60	268	250	48	535	285	240	1.558	1.158	16.5	14.9
L2	A1	盒装	4	40	268	250	48	535	285	240	1.585	1.185	16.8	15.2

包装形态
PACKING

封装型号 Package No	包装代码 Packing Code	包装方式 Packing Method	只/盒 Pcs/Box	只/箱 Pcs/Carton	内盒尺寸(mm) Inner Box Size			外箱尺寸(mm) Carton Size			单盒重量(±0.3Kg) Single box weight		整箱重量(±0.5Kg) FCL weight	
					长(L)	宽(W)	高(H)	长(L)	宽(W)	高(H)	毛重(KG)	净重(KG)	毛重(KG)	净重(KG)
E3	A1	盒装	6	42	385	285	30	410	300	255	2.35	2.2	15	14
E1	A1	盒装	10	70	385	285	30	410	300	255	2	1.95	15	14
E1A	A1	盒装	10	70	385	285	30	410	300	255	2	1.95	15	14
E2A	A1	盒装	6	42	385	285	30	410	300	255	2	1.95	15	14
E2	A1	盒装	6	42	385	285	30	410	300	255	2	1.95	15	14
P2	A1	盒装	24	240	357	277	29	410	300	255	0.75	0.7	7	6
P3	A1	盒装	16	128	357	277	29	410	300	255	1	0.95	9	8
TO-3P	A1	盒装	420	2100	555	135	55	575	295	155	4	2.6	20	12.8
TO-247	A1	盒装	330	1980	522	100	52	535	220	178	2.7	2.16	16.72	13.02
TO-220F	A2	管装	1000	5000	565	170	53	580	285	187	2.95	2.17	14.15	10.85
TO-263	A2	编带	800	4000	362	347	51	381	364	295	1.95	1.55	10.65	7.75
TO-220	A2	管装	1000	5000	565	170	53	580	285	187	2.95	2.06	15.35	10.3

可靠性试验项目
RELIABILITY TEST ITEM

序号	试验项目 Test Item	试验条件 Condition	抽样数 (Sample size)	判定标准 (Decision)	试验依据 (Reference)
1	高温反偏 (High Temperature Reverse Bias)	a、Voltage：80% Rated Voltage; b、Time：168h/1000h; c、Temperature：Fast Recovery Diode or Thyristor：125℃; Discrete Device,MOSFET or IGBT：145℃; Rectifier Diode：150℃.	5PCS（FG）	LSL≤Electrical Parameter≤USL	IEC 60747
2	高温栅偏 (High Temperature Grating Bias)	a、Voltage： ±VGSmax/VGEmax; b、Temperature：Tstgmax ; c、Time：168h/1000h.	5PCS（FG）	LSL≤Electrical Parameter≤USL	IEC 60747
3	温度循环 (Temperature Cycling)	a、Temperature：Low Temperature -55℃ for 30min; High Temperature 150℃ for 30min; b、Conversion Time：10s; c、Cycle Times：10Times/100Times.	5PCS（FG）	LSL≤Electrical Parameter≤USL	IEC 60068-2-14 Test Na
4	恒温恒湿 (Constant Temperature and Humidity)	a、Temperature：85℃; b、Humidity：85% RH; c、Time：168h/1000h.	5PCS（FG）	LSL≤Electrical Parameter≤USL	IEC 60068-2-67
5	功率循环 (Power Cycling)	a、ΔTJ=100℃+15/-10℃; b、Cycle Times：100Times/1000Times.	5PCS（FG）	LSL≤Electrical Parameter≤USL	IEC 60749-34
6	高温存储 (High Temperature Storage)	a、Temperature：Tstgmax ; b、Time：168H/1000H.	5PCS（FG）	LSL≤Electrical Parameter≤USL	IEC 60068-2-2
7	低温存储 (Low Temperature storage)	a、Temperature：Tstgmin; b、Time：168H/1000H.	5PCS（FG）	LSL≤Electrical Parameter≤USL	IEC 60068-2-1
8	冲击试验 (Shock Test)	a、Max.：50G; b、Pulse Time：6ms,Sine Half Wave; c、Dir.: X / Y / Z，3 Positive and 3 Negative Impacts, 18Times in total.	5PCS（FG）	LSL≤Electrical Parameter≤USL	IEC 60068-2-27 Test Ea
9	震动试验 (Vibration Test)	a、Vibration Waveform：5~200 Hz,Sine Wave; b、Acceleration: 5g; c、Direction of Vibration：x, y, z; d、Vibration Time：Frequency Sweep：5Hz~200Hz~5Hz, 1min, 2H per axle.	5PCS（FG）	LSL≤Electrical Parameter≤USL	IEC 60068-2-6 Test Fc

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